

APPROVED	O.G. FIG.	
BY	CLASS	SUBJECT
DRAFTSMAN		



Point Curvature: Large
 Aspect Ratio: Small ($\div 1$)

FIG. 1A PRIOR ART



Point Curvature: Little Small
 Aspect Ratio: Small ($\div 4.5$)

FIG. 1B PRIOR ART



Point Curvature: Little Small
 Aspect Ratio: Small ($\div 1$)

FIG. 1C PRIOR ART

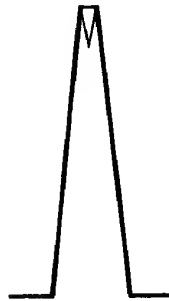
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APPROVED	O.G. FIG.	
BY	CLASS	SUBCL.
DRAFTSMAN		



Point Curvature: Small (Several nm)
Aspect Ratio: Large ($\div 10$)

FIG. 1D PRESENT INVENTION



Point Curvature: Small (Several nm)
Aspect Ratio: Large ($\div 10$)

FIG. 1E PRESENT INVENTION

66307-12302100

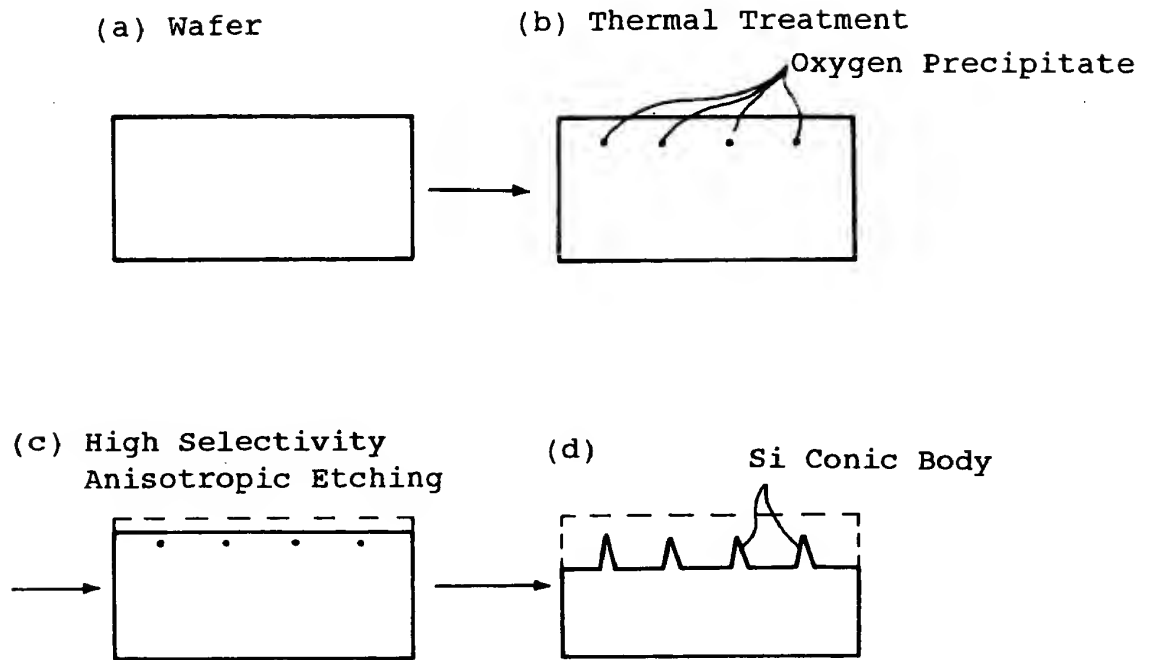


FIG. 2

FIG. 3A

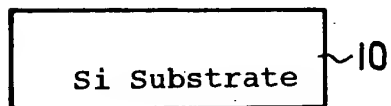


FIG. 3B

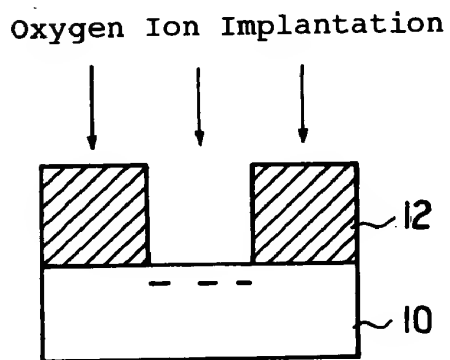


FIG. 3C

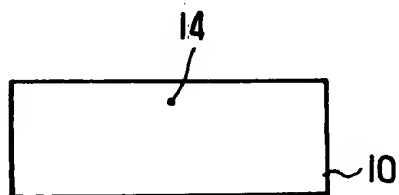
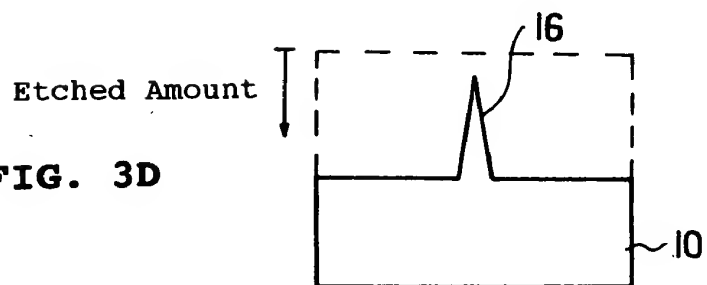


FIG. 3D



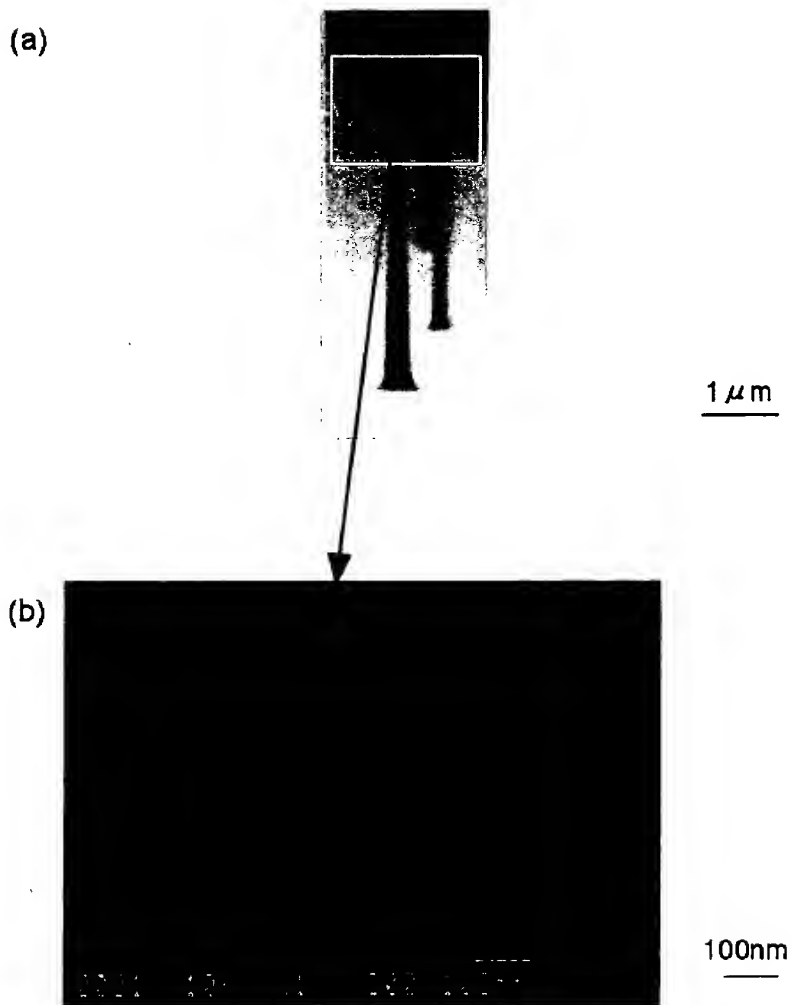


FIG. 4

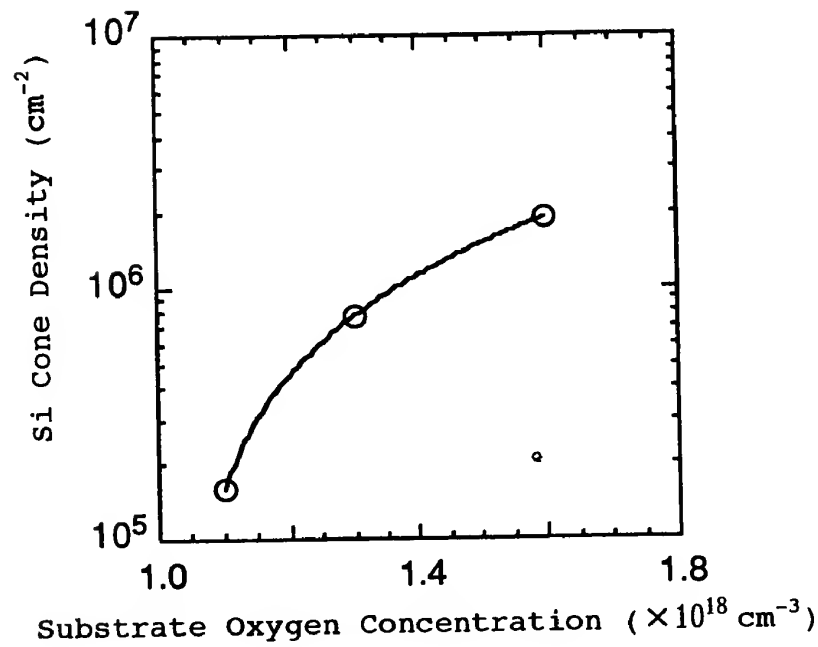


FIG. 5

0068-039-0

100 & III

Black dots are $\frac{100\mu m}{\text{silicon needle conic bodies.}}$

FIG. 6B

APP. NO. D.G. FIG.
CLASS. SUBC.
DRAWING

FIG. 7A

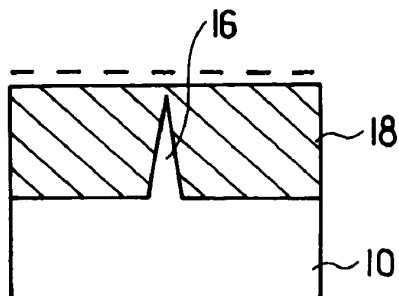


FIG. 7B

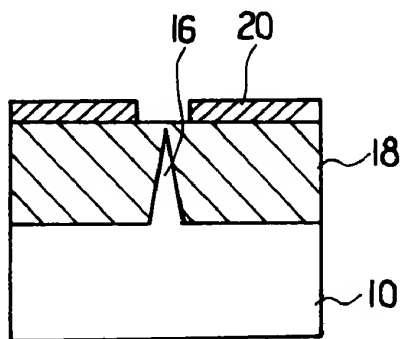
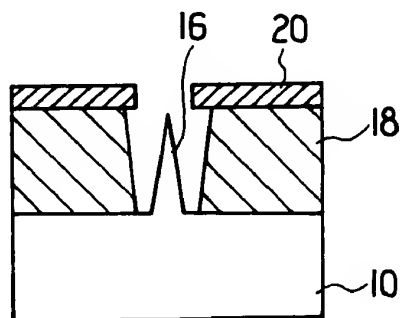


FIG. 7C



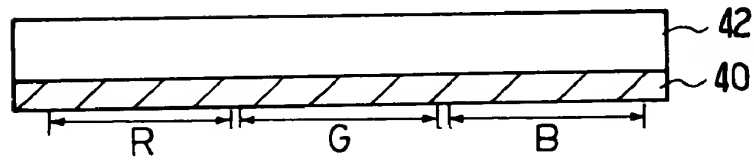


FIG. 8A

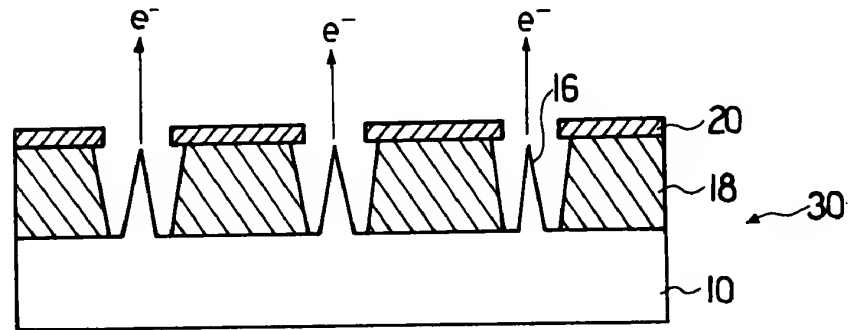
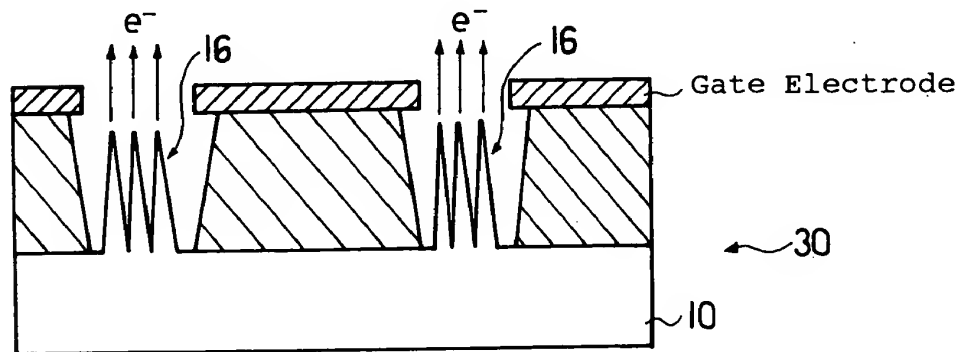
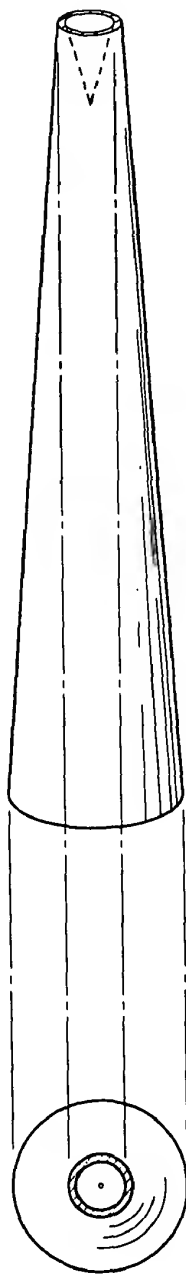


FIG. 8B



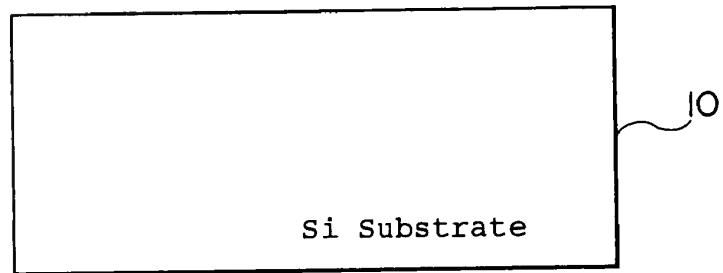
(a)



(b)

FIG. 9

FIG. 10A



Oxygen Ion Implantation



FIG. 10B

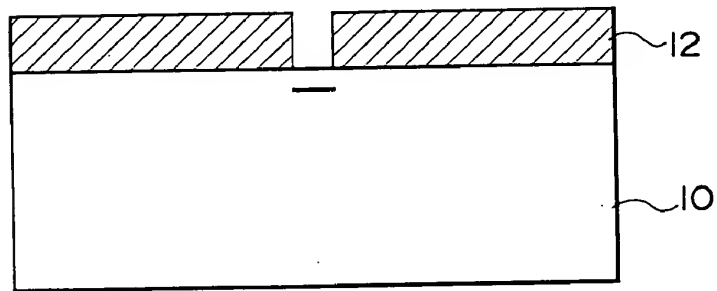
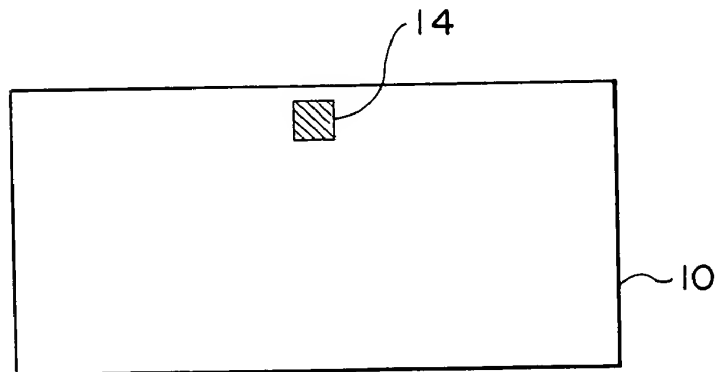
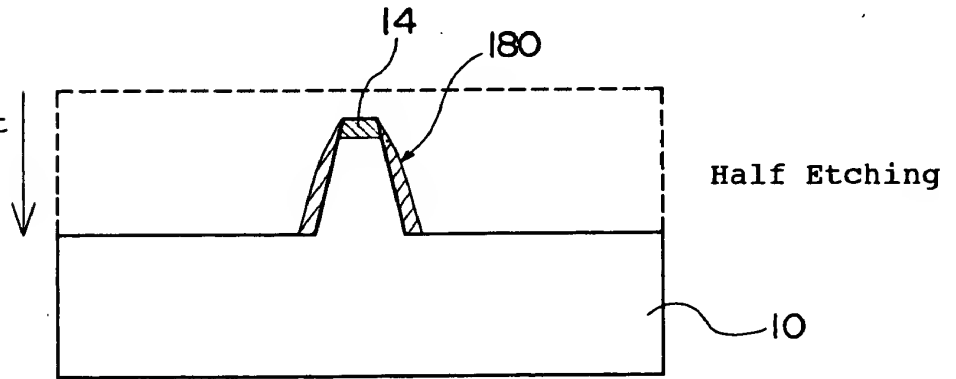


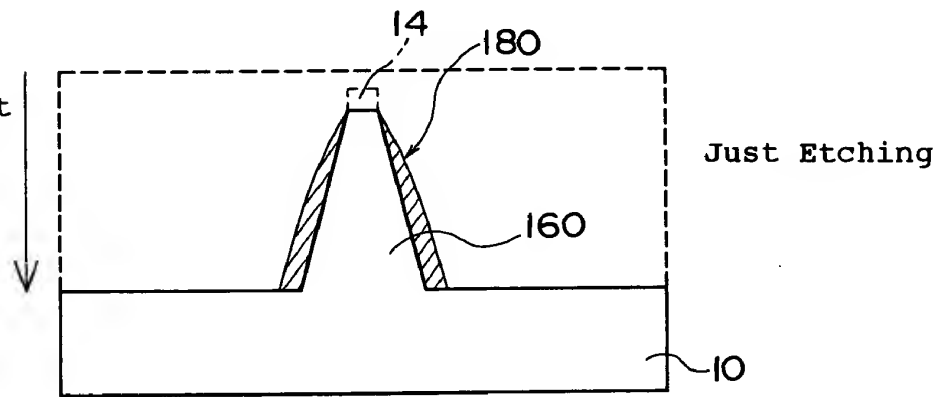
FIG. 10C



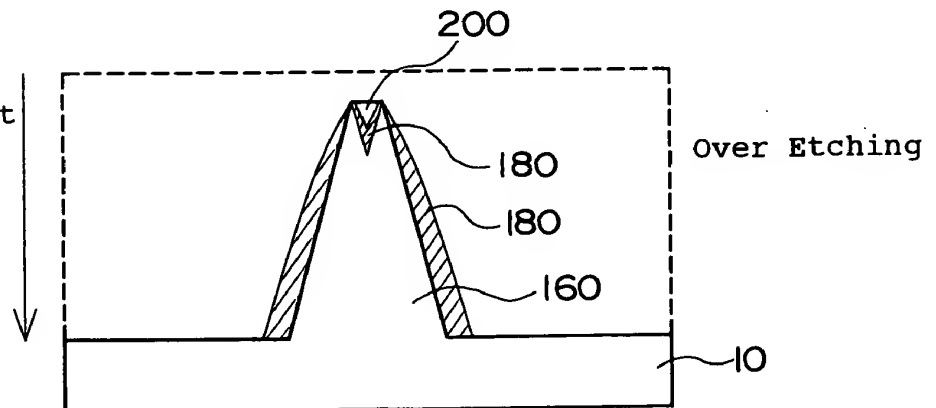
Etched Amount
FIG. 10D



Etched Amount
FIG. 10E



Etched Amount
FIG. 10F



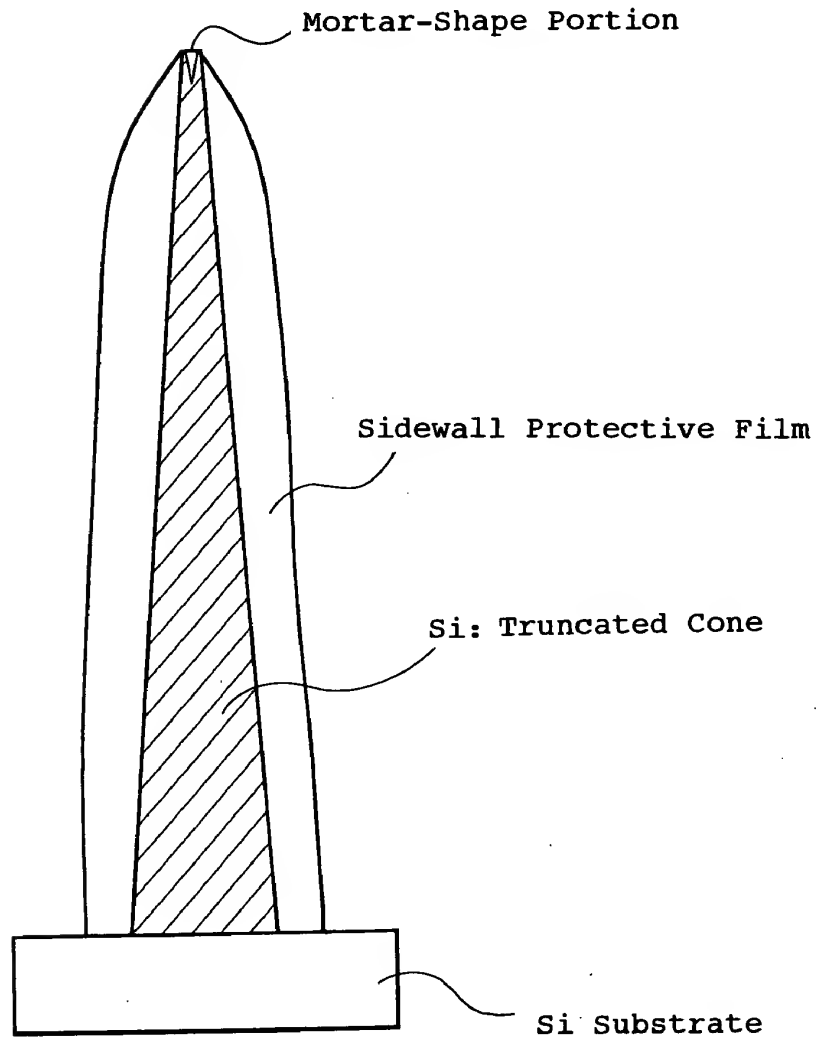


FIG. 11

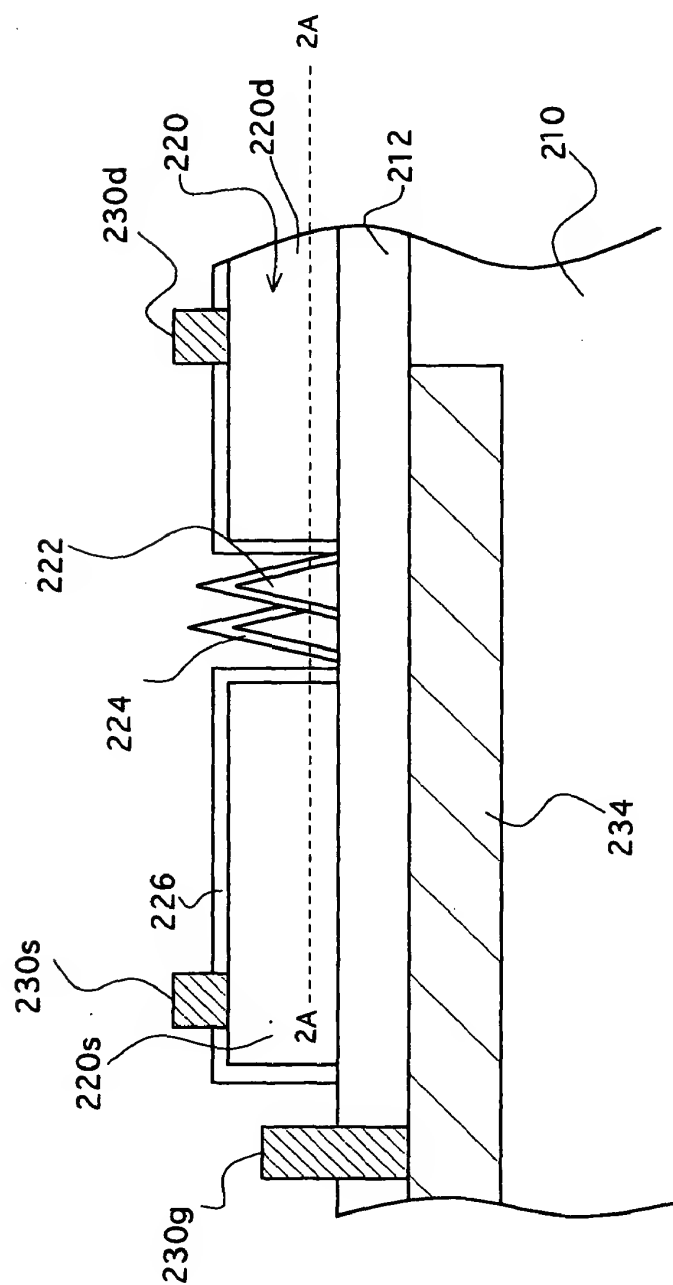


FIG. 18

FIG. 12A

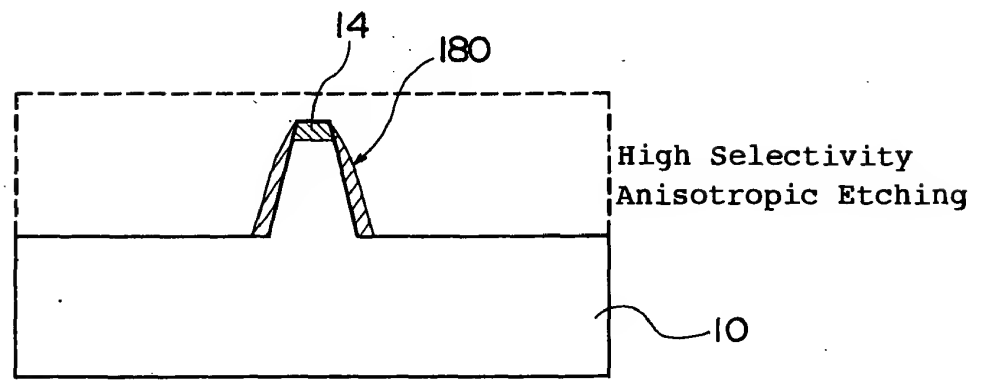


FIG. 12B

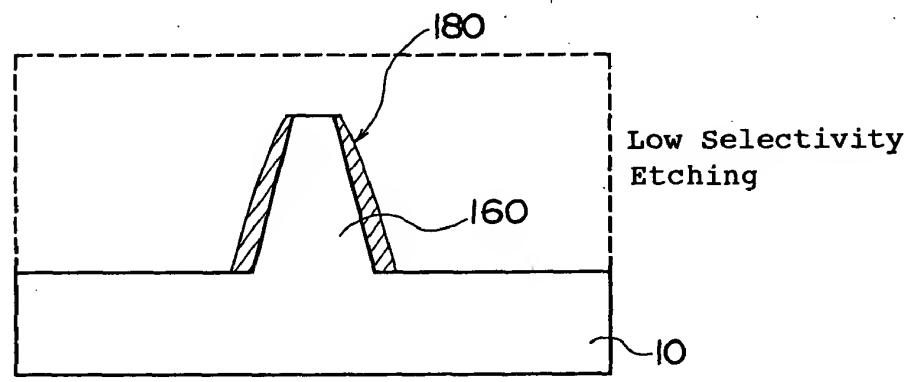


FIG. 12C

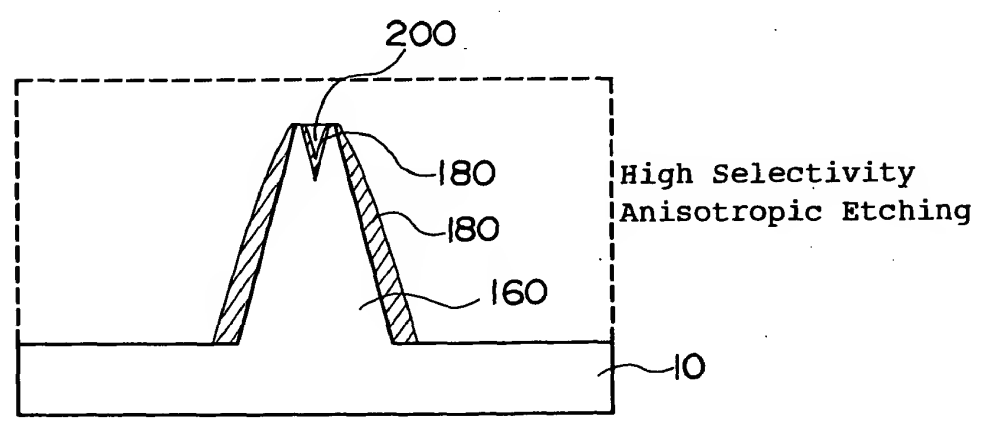


FIG. 13A

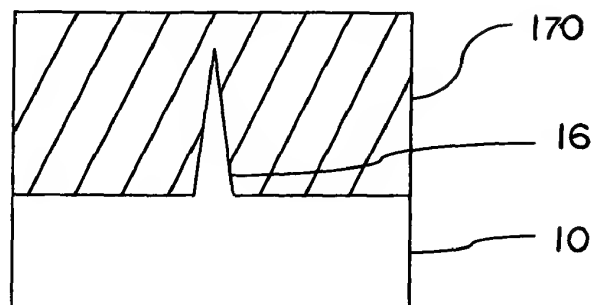


FIG. 13B

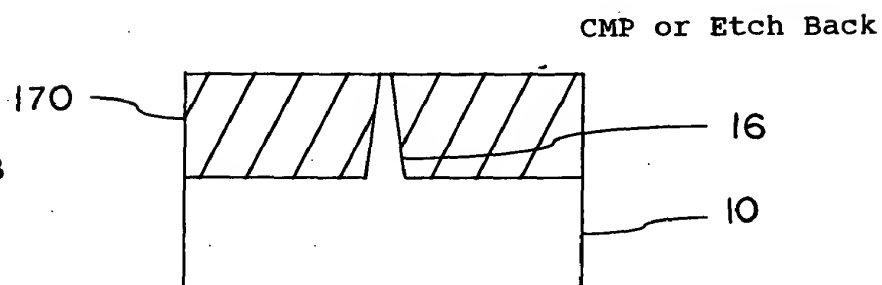


FIG. 13C

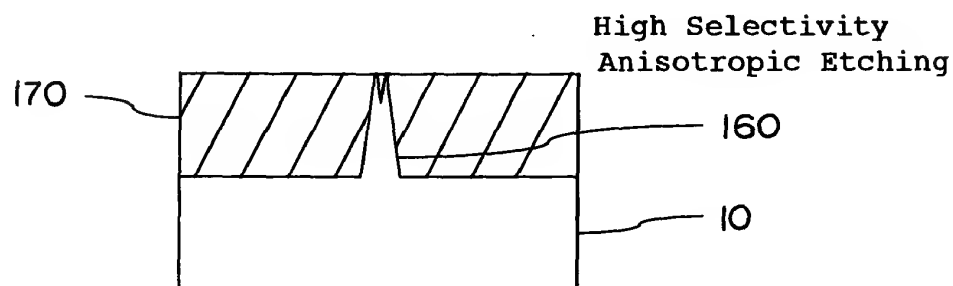
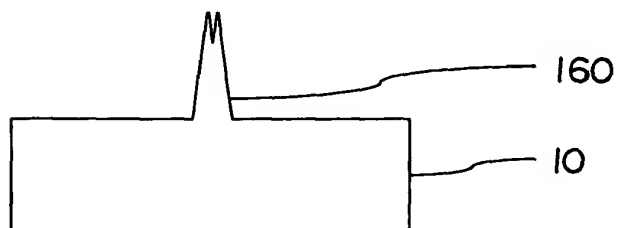


FIG. 13D



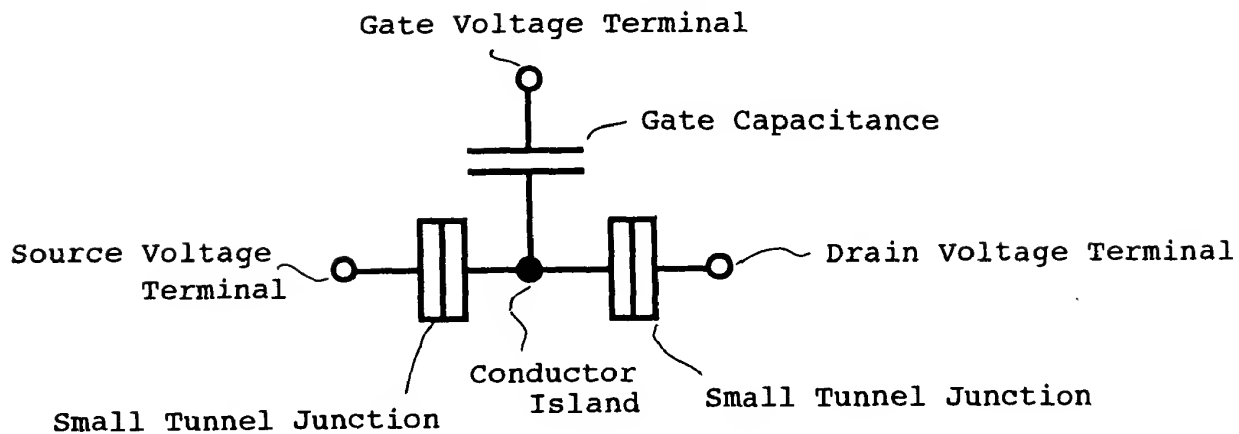


FIG. 14A PRIOR ART

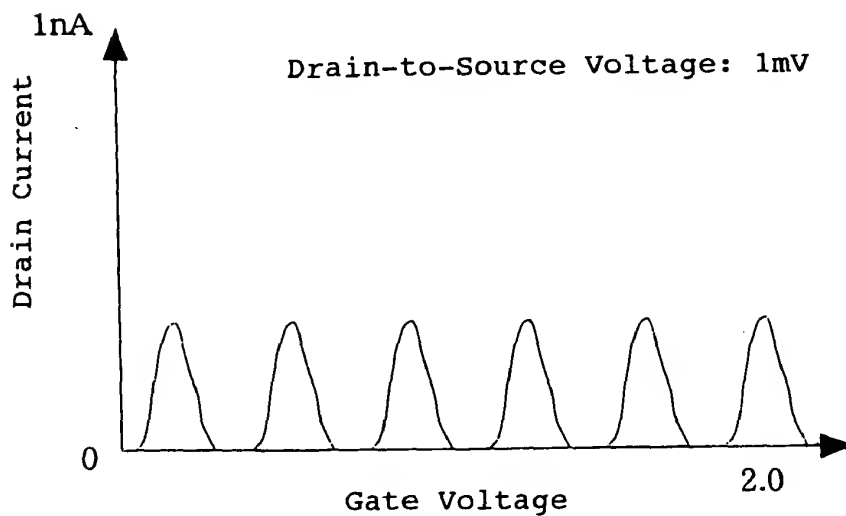


FIG. 14B PRIOR ART

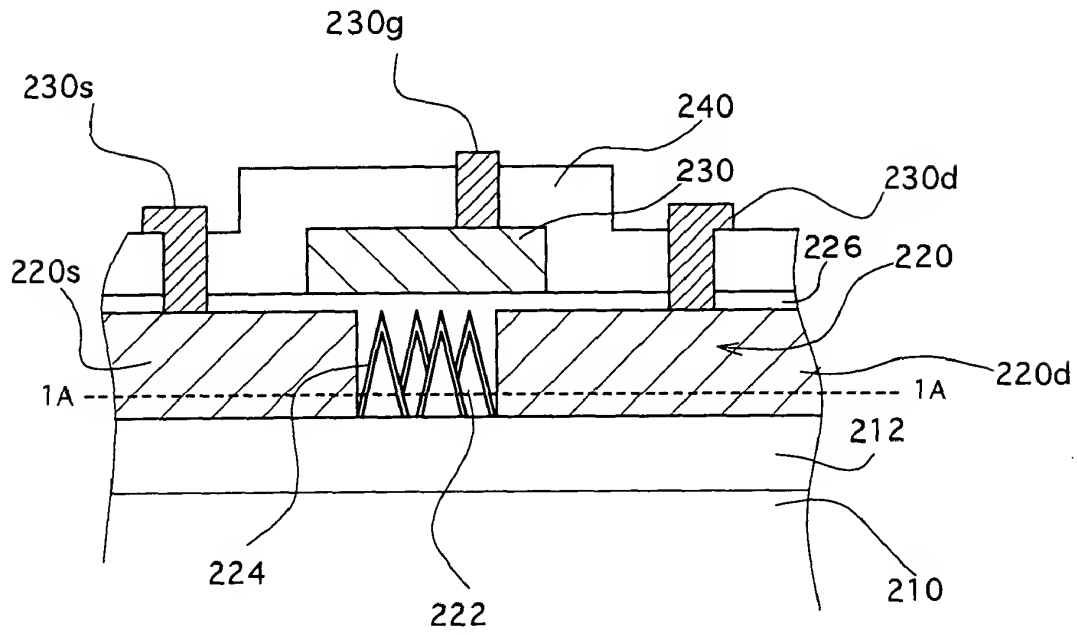


FIG. 15A

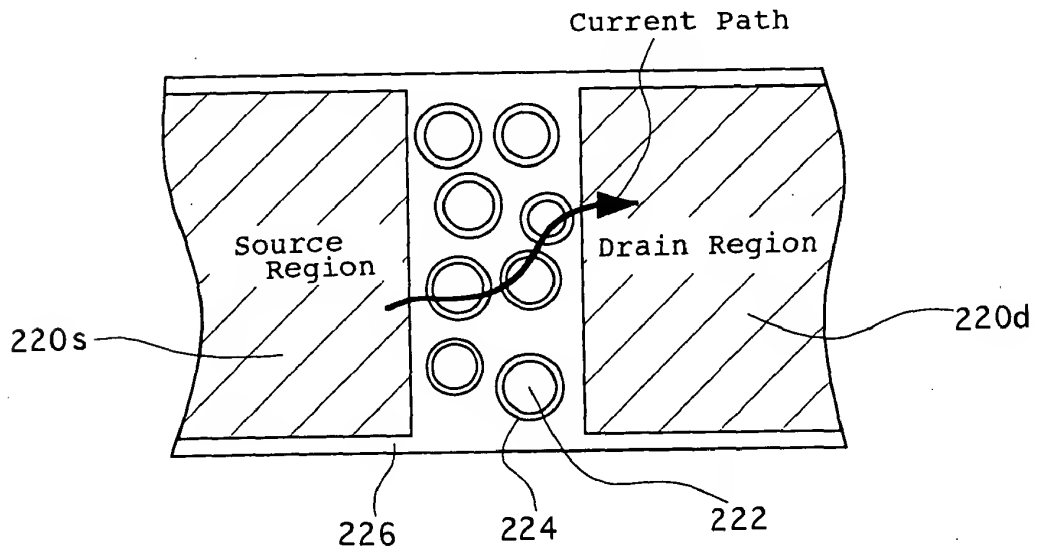
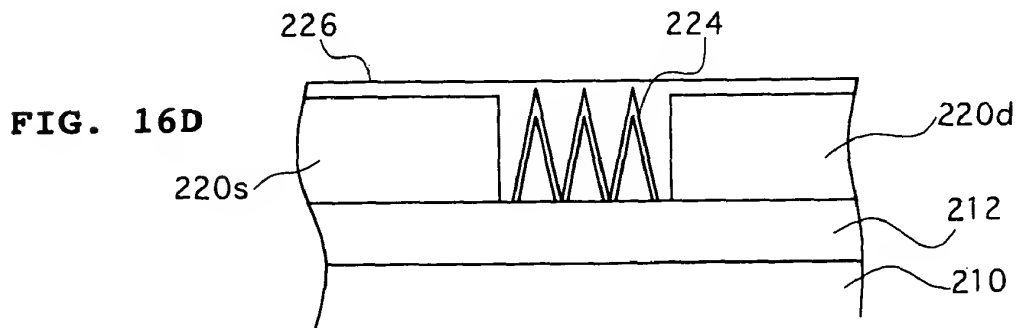
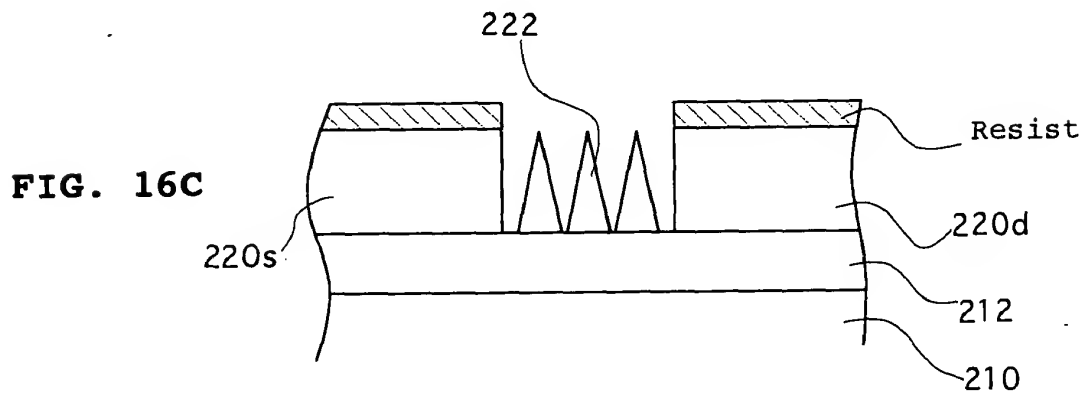
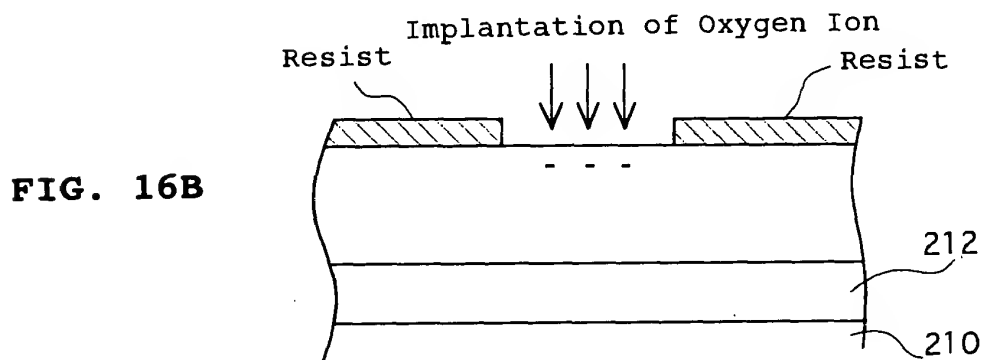
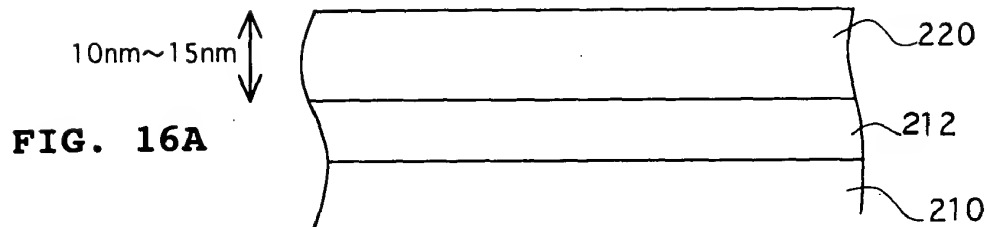


FIG. 15B



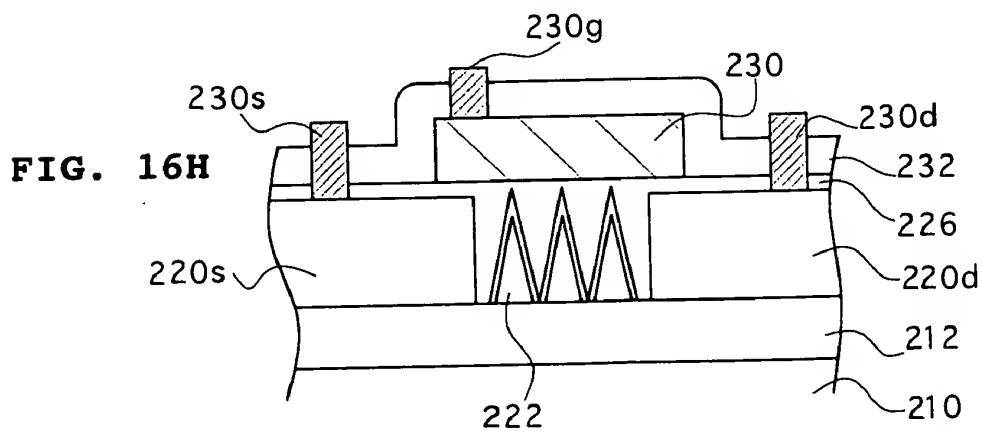
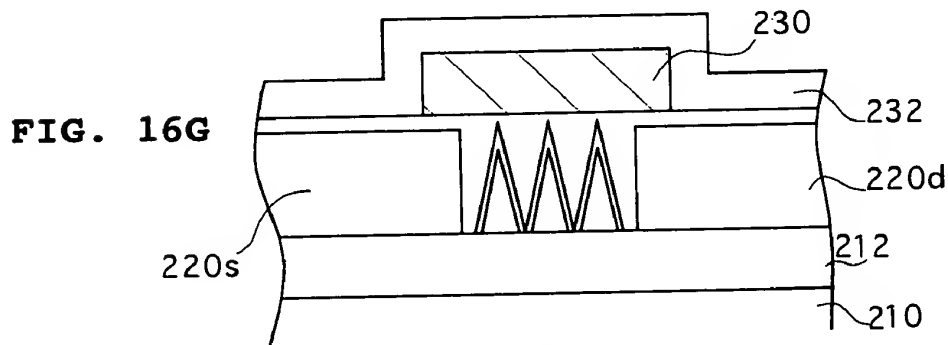
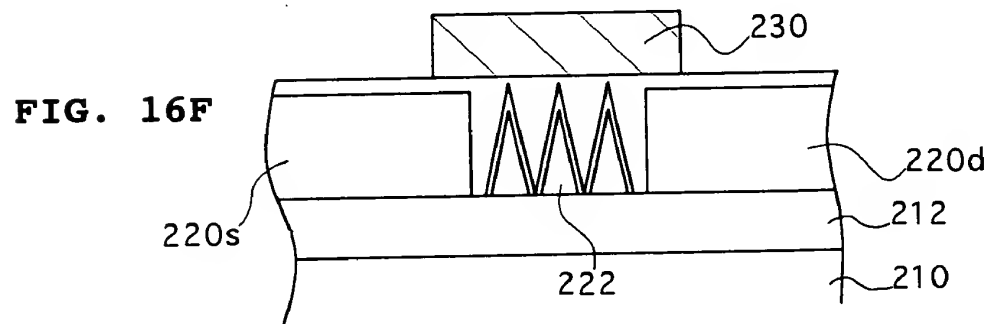
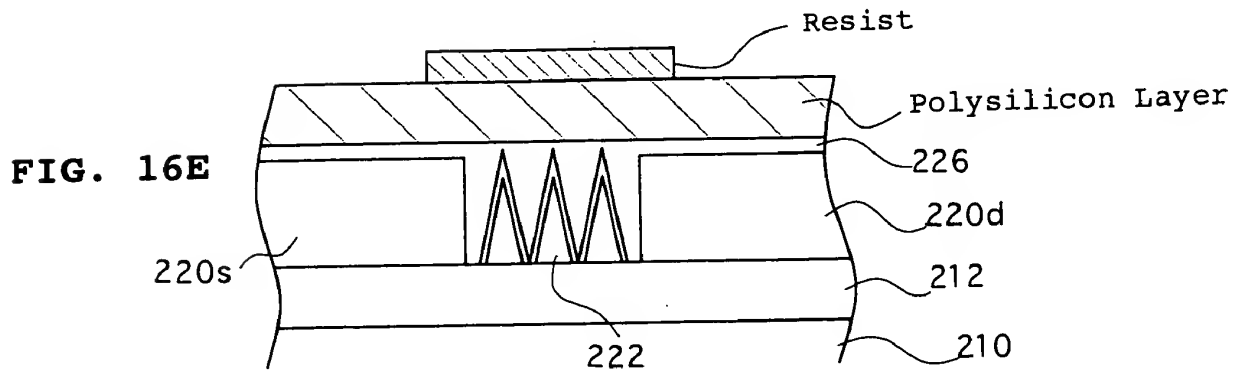
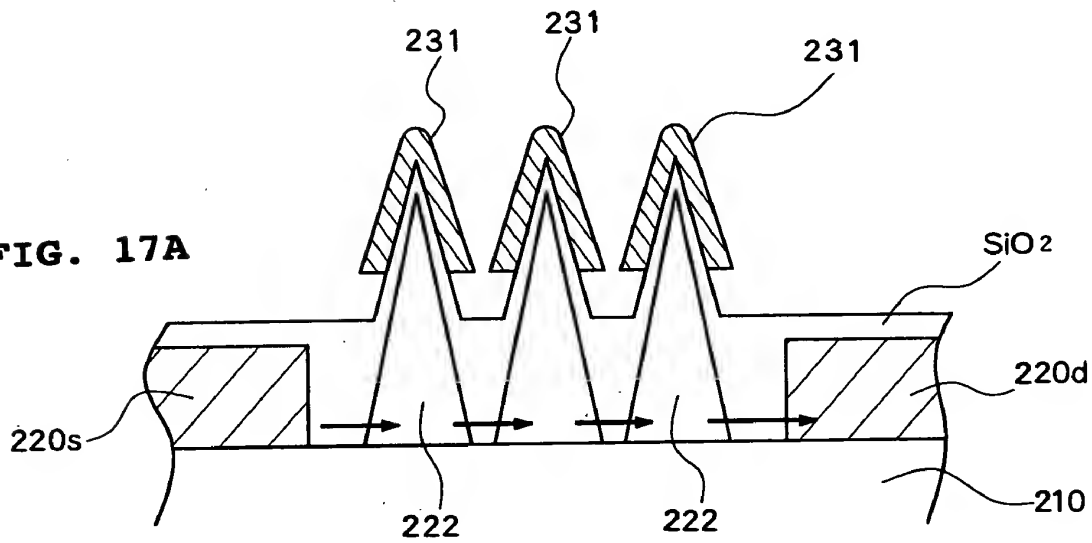


FIG. 17A



Selective Gate Control

FIG. 17B

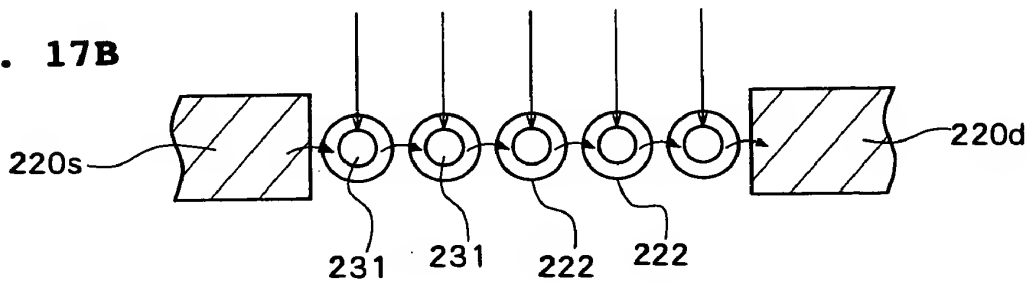
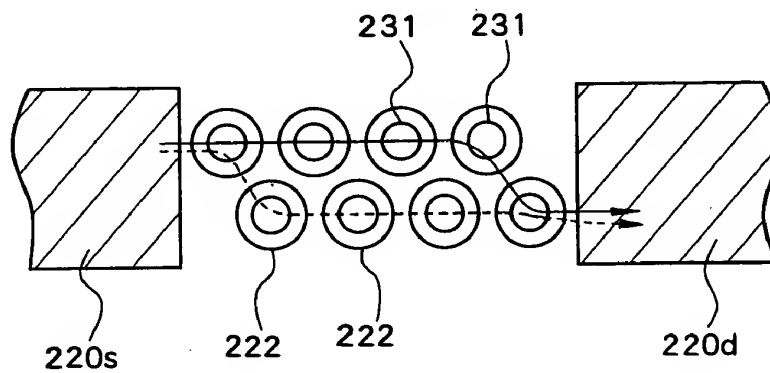


FIG. 17C



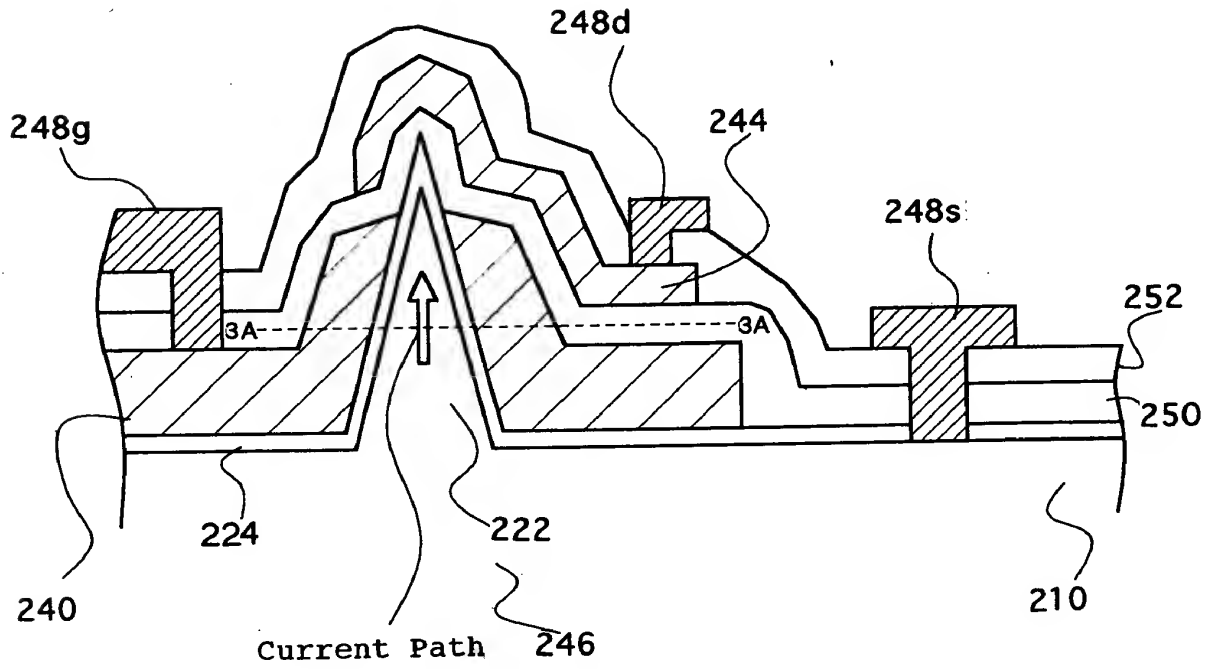


FIG. 19A

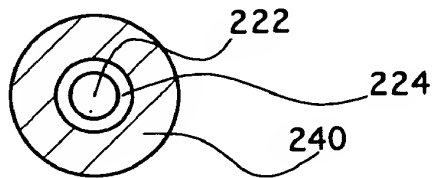
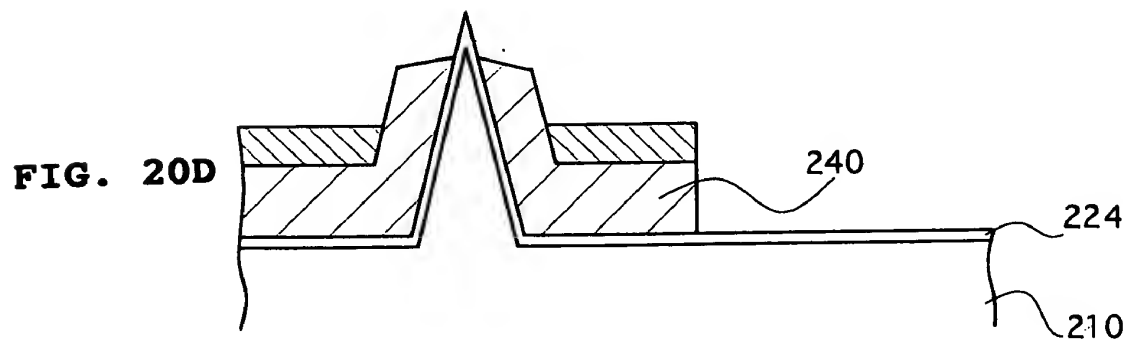
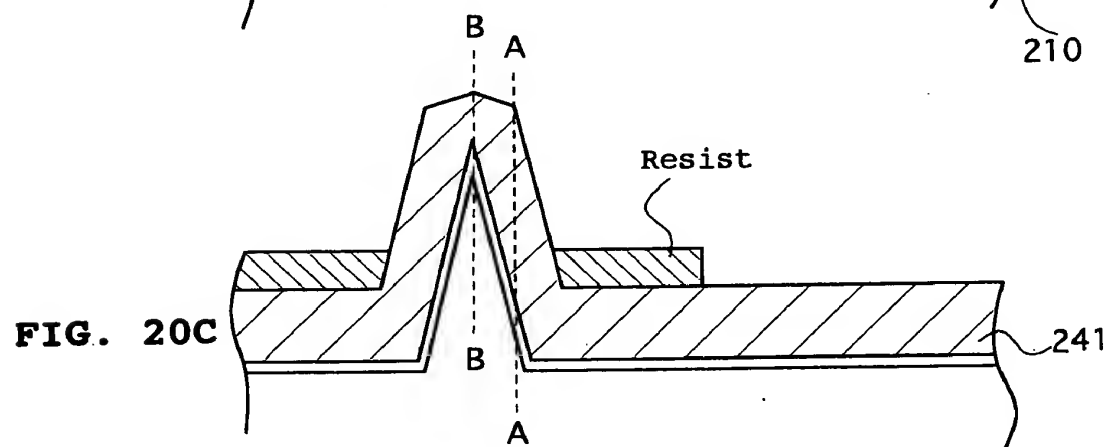
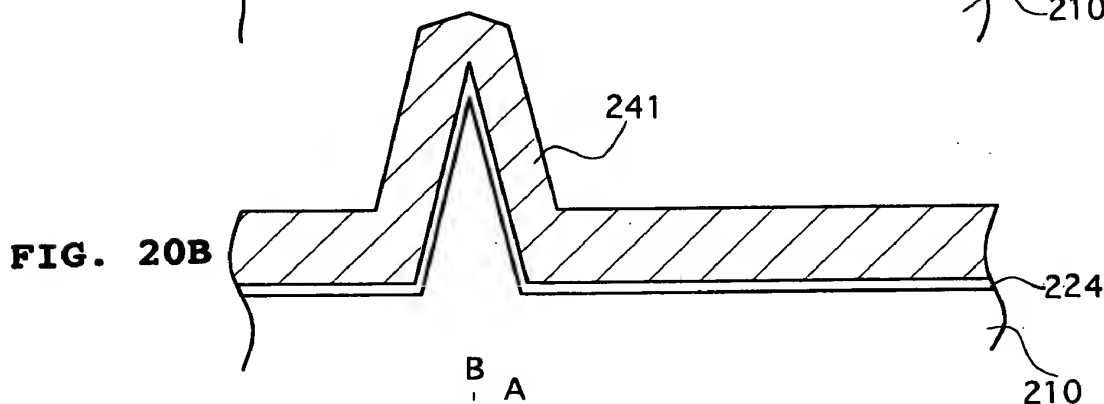
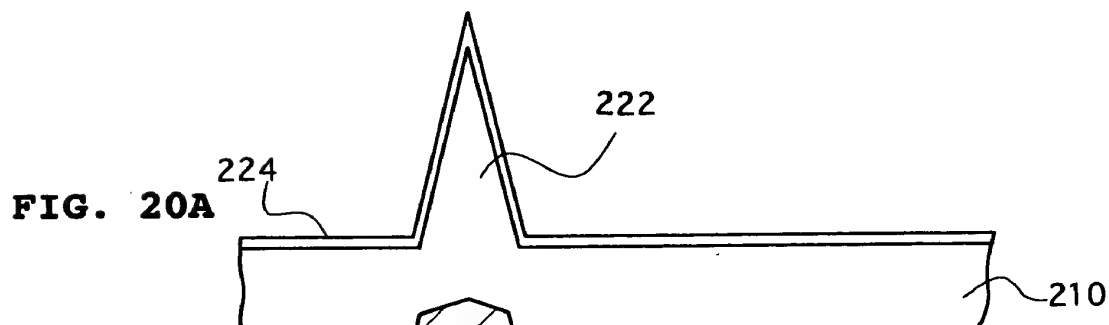


FIG. 19B



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FIG. 20E

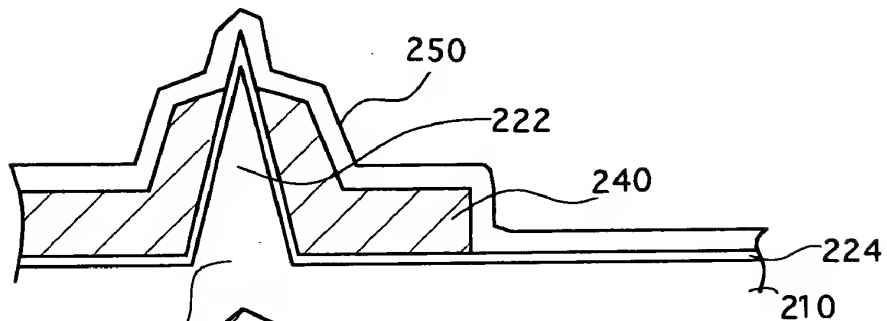


FIG. 20F

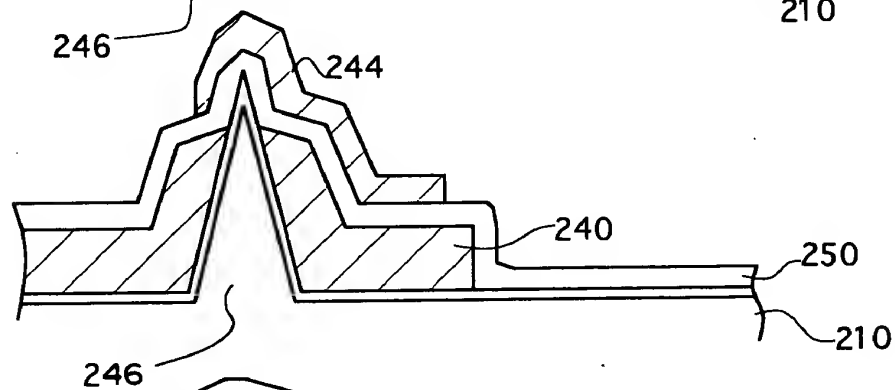


FIG. 20G

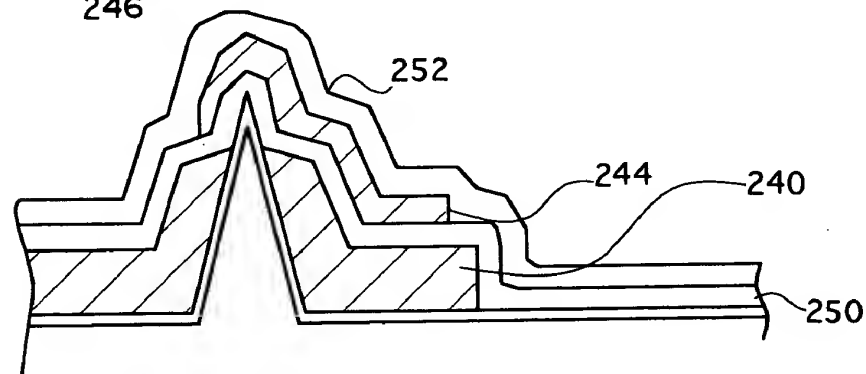


FIG. 20H

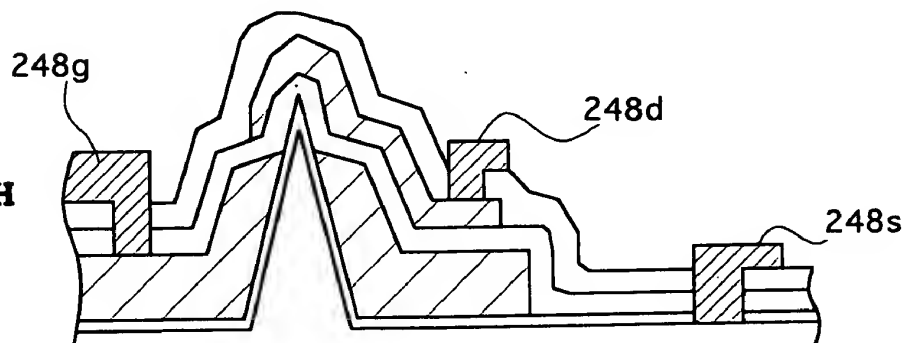


FIG. 21

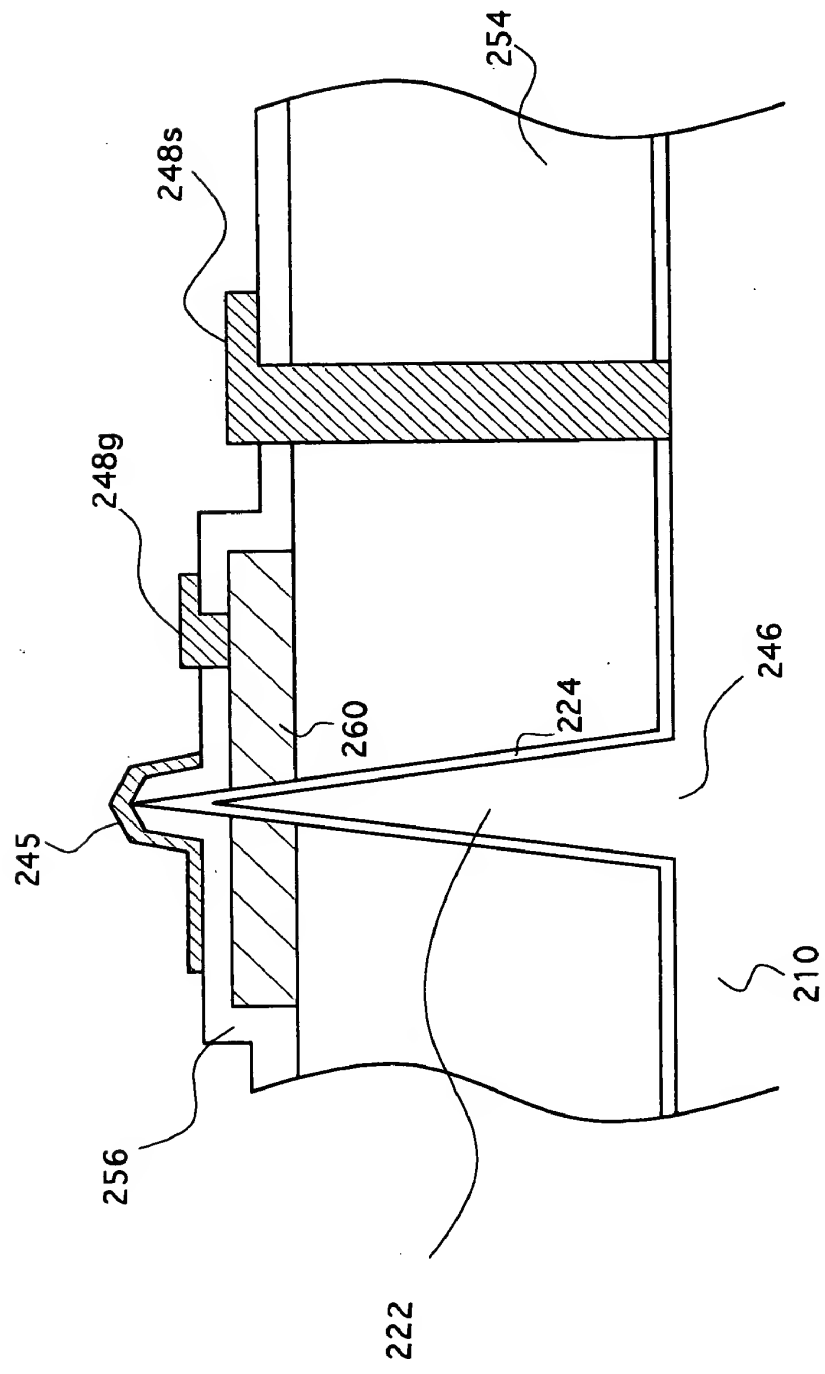


FIG. 21

FIG. 22

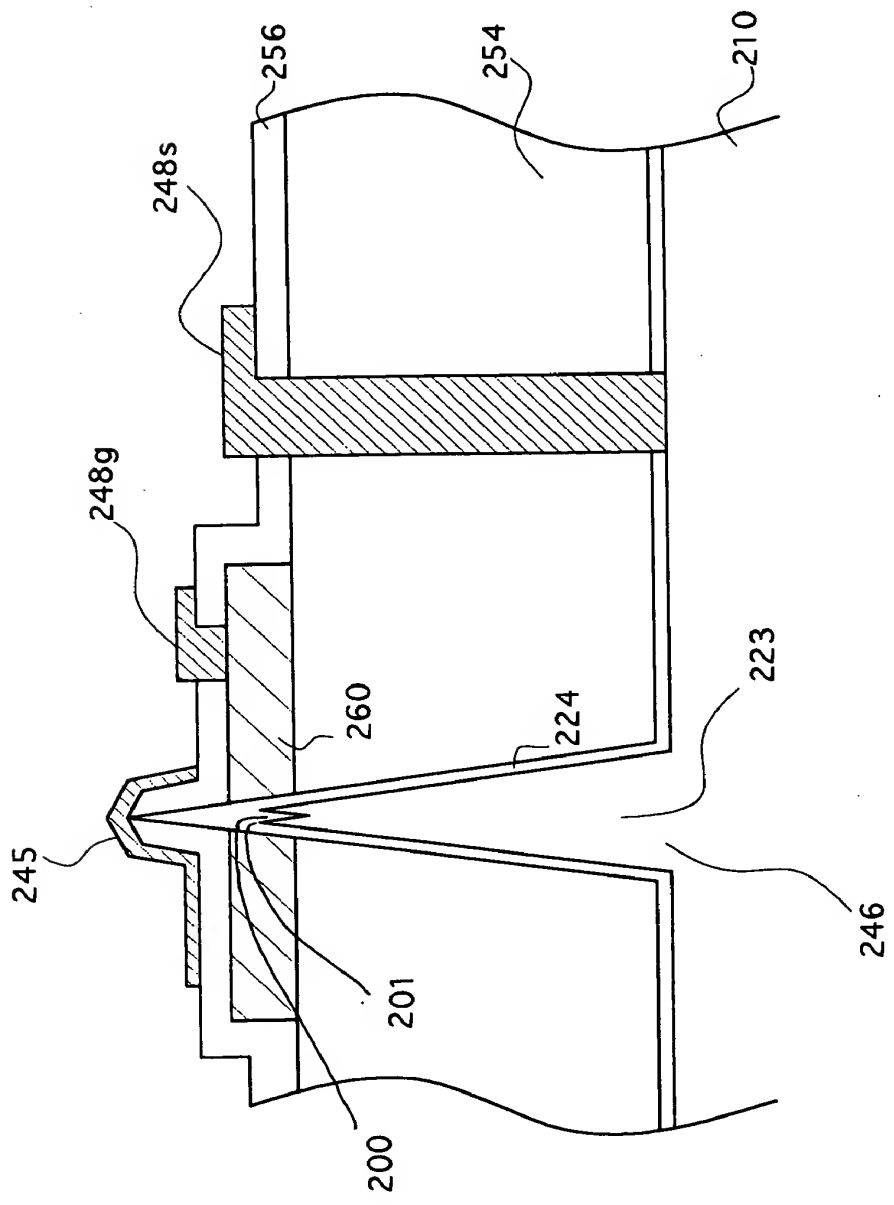


FIG. 22

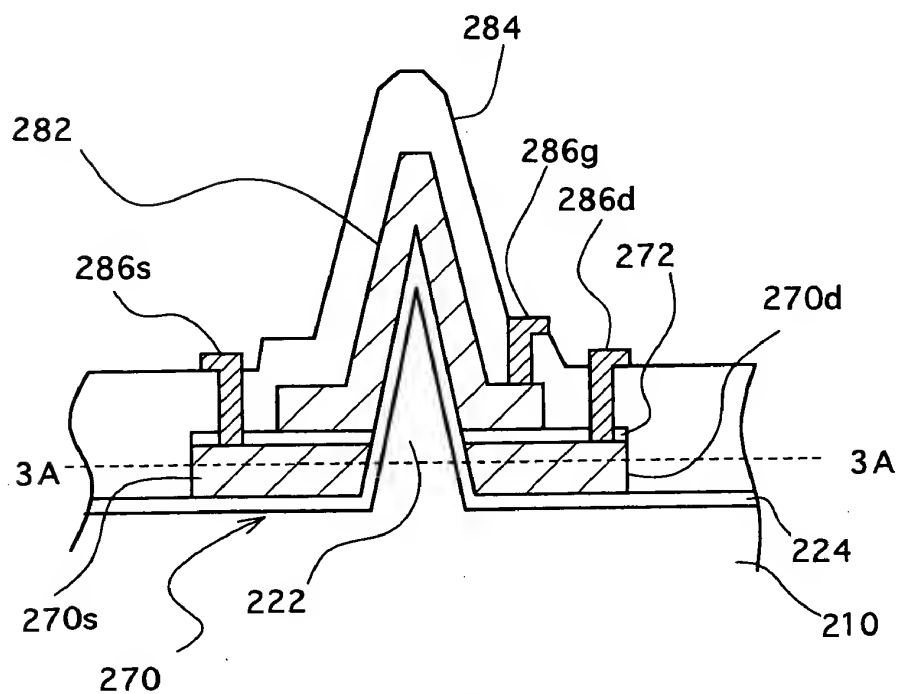


FIG. 23A

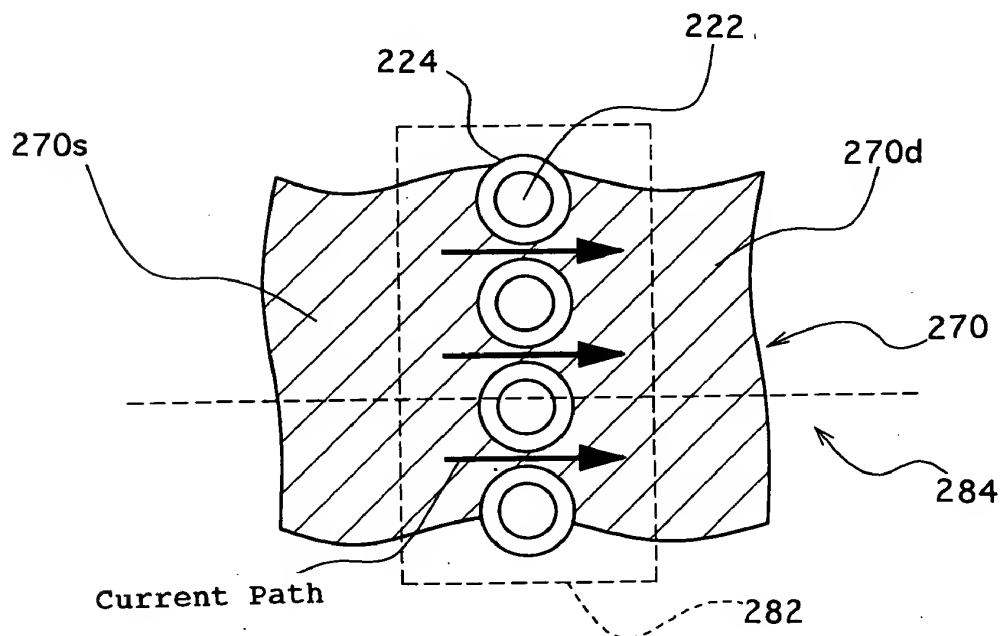


FIG. 23B

FIG. 24A

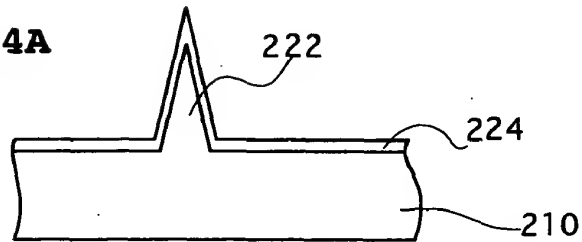


FIG. 24B

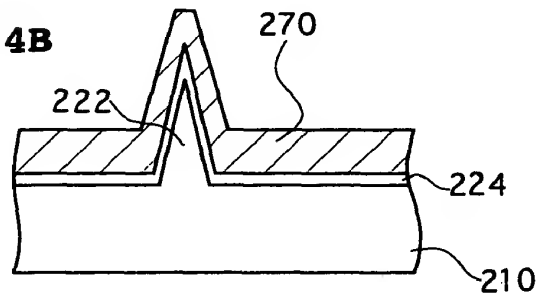


FIG. 24C

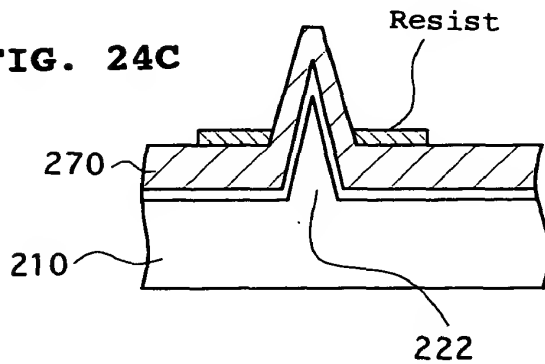


FIG. 24D

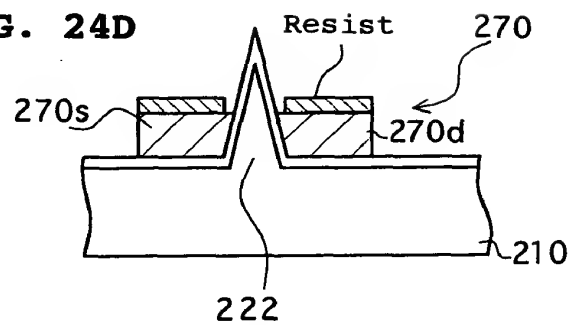
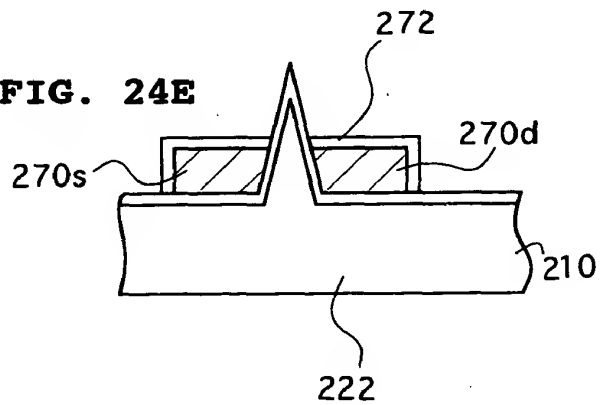
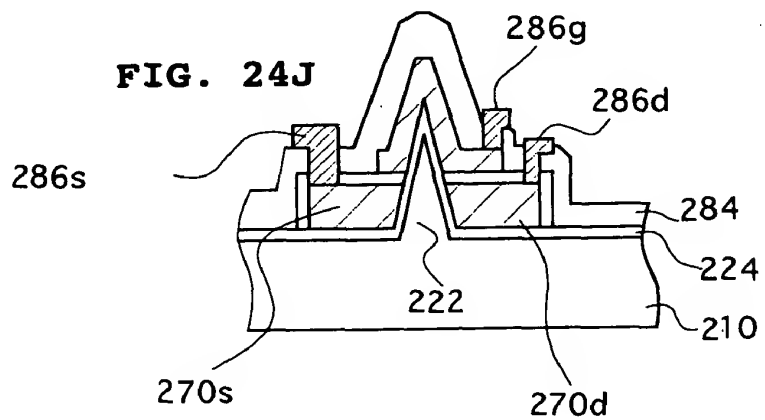
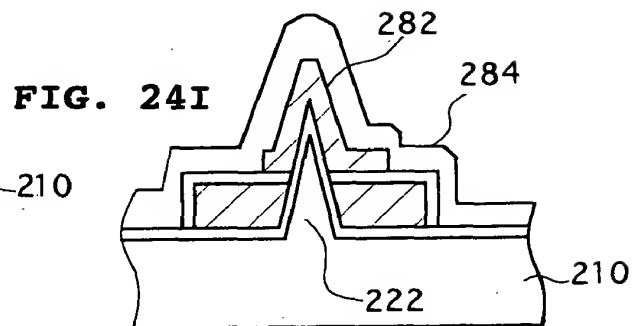
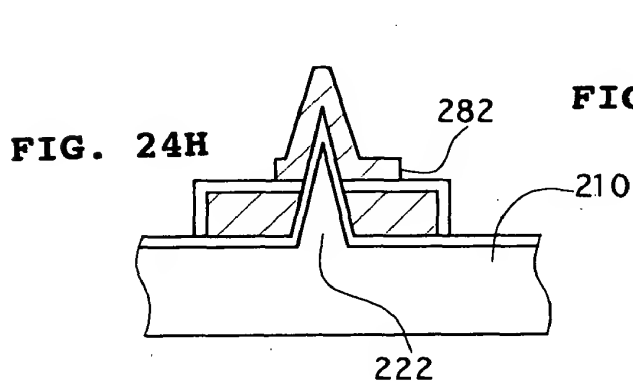
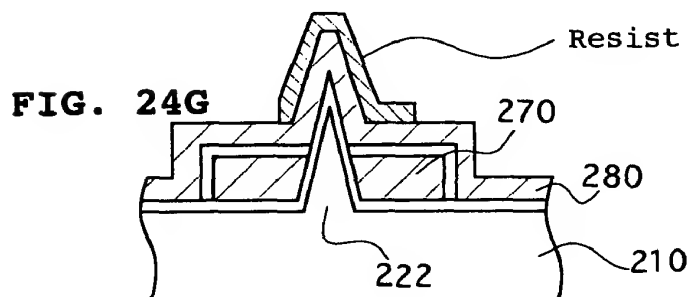
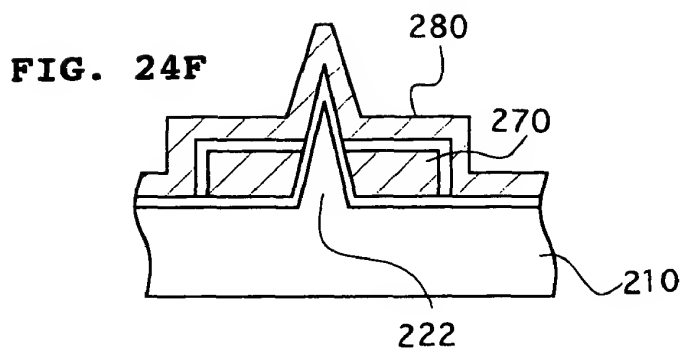


FIG. 24E





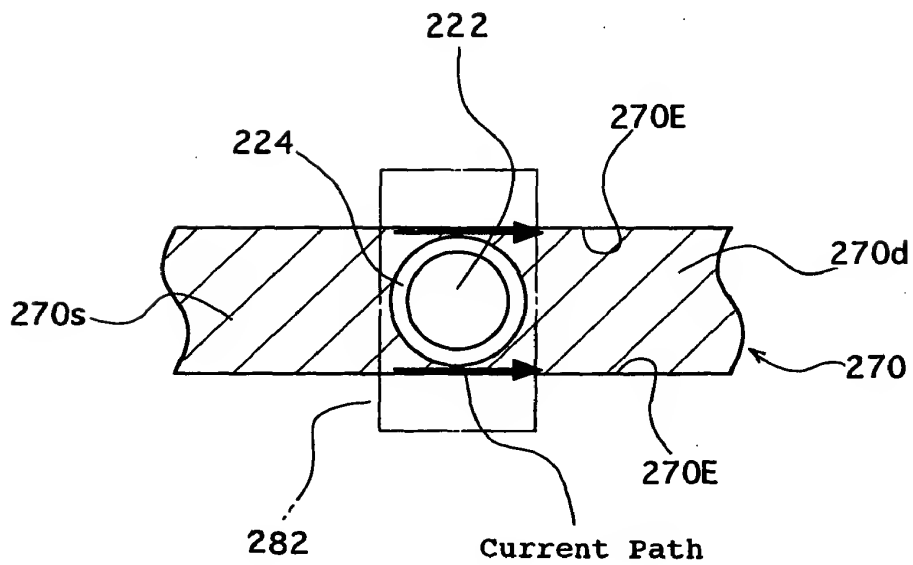


FIG. 25A

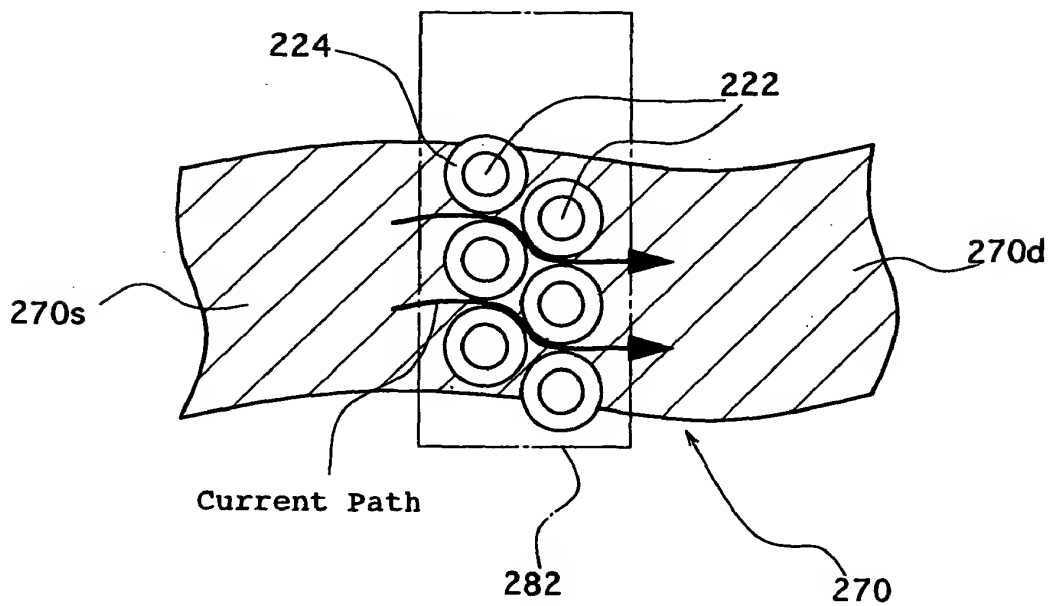


FIG. 25B

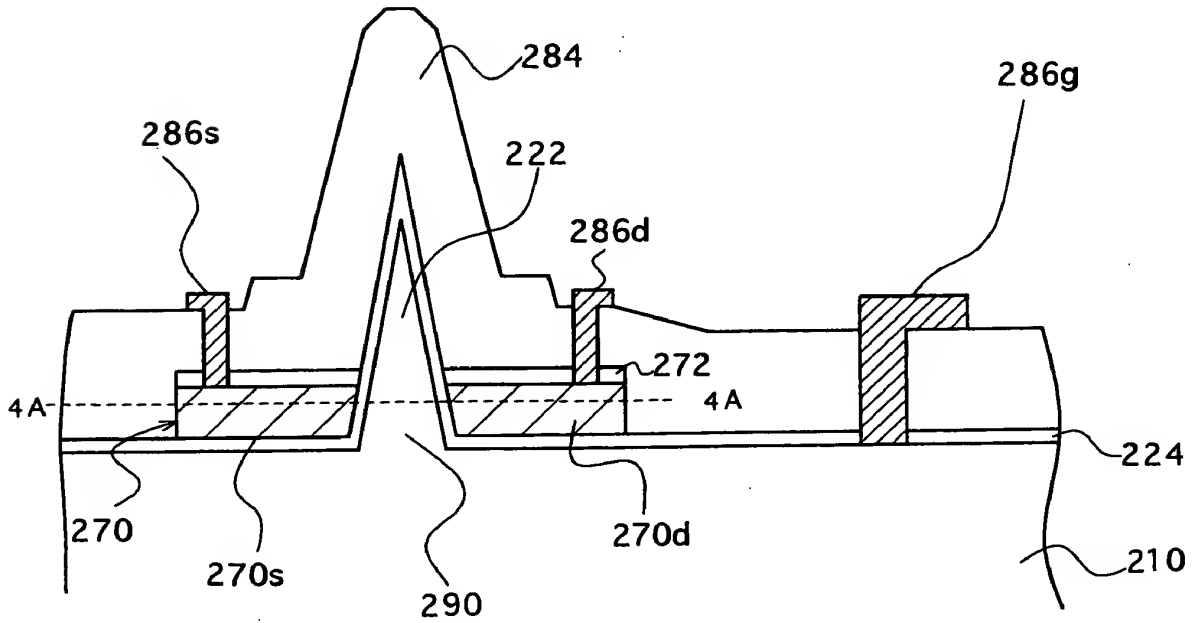


FIG. 26A

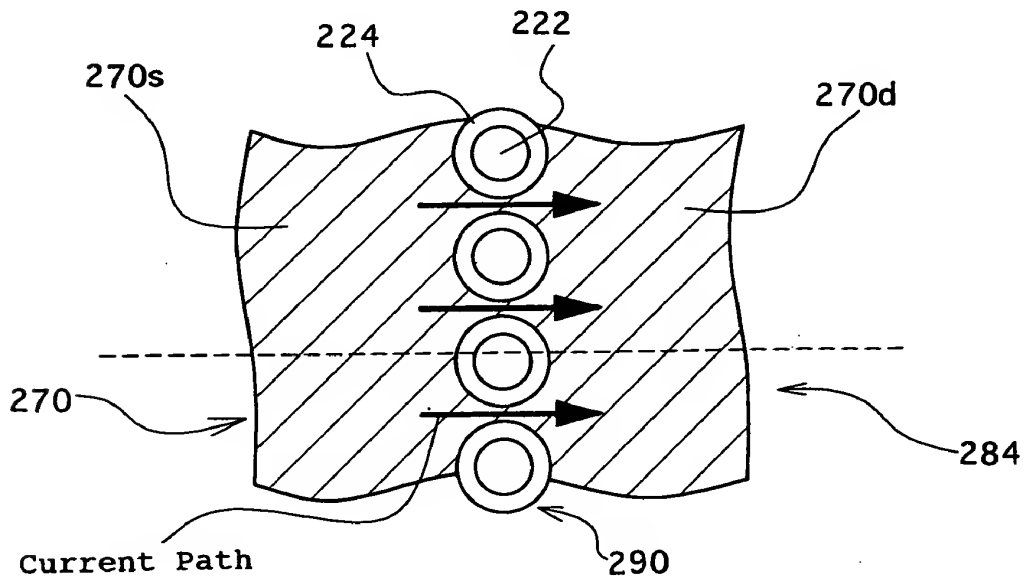


FIG. 26B

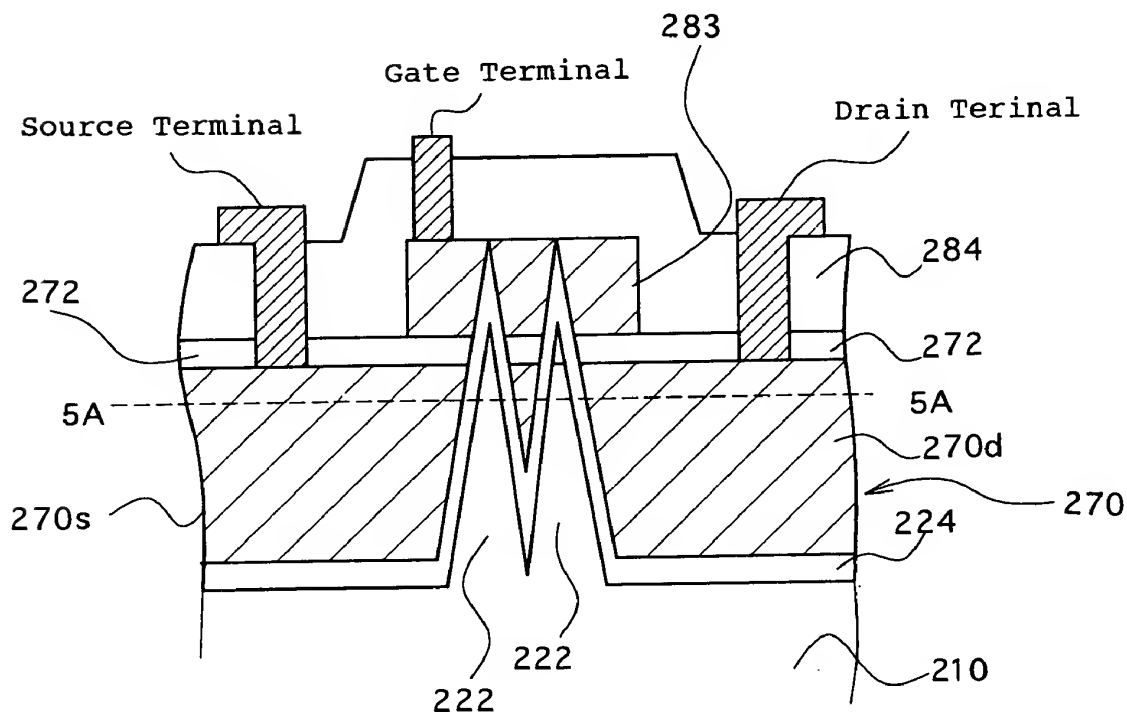


FIG. 27A

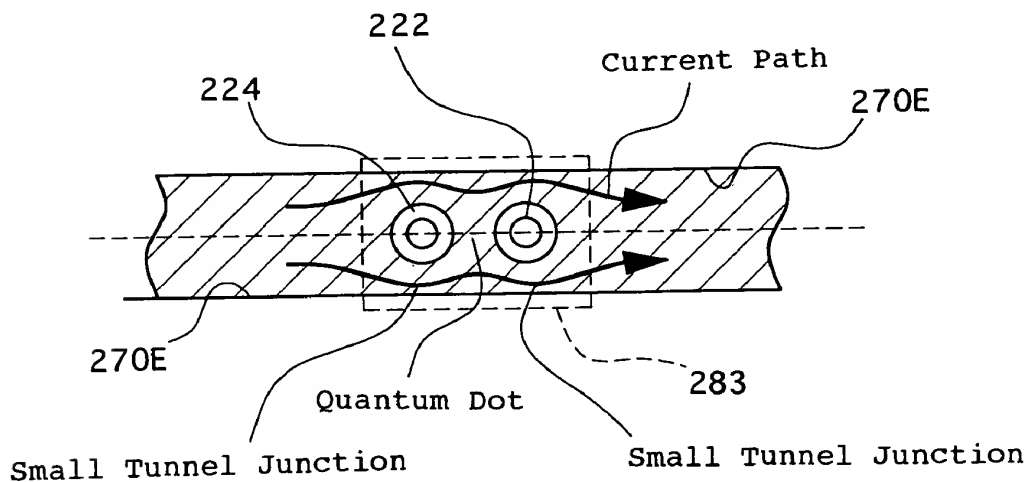


FIG. 27B

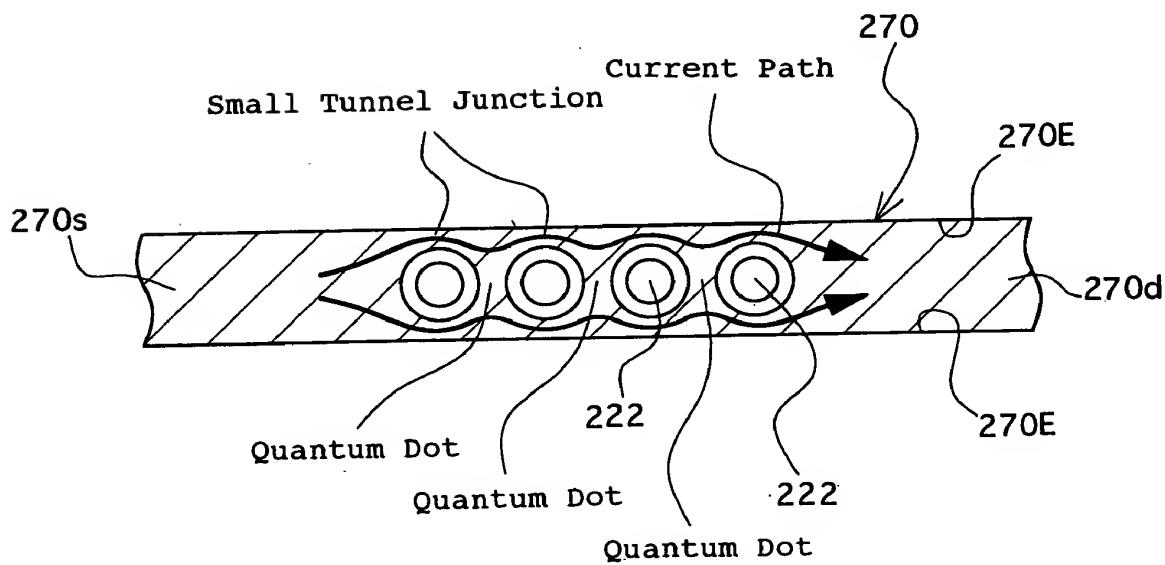


FIG. 28

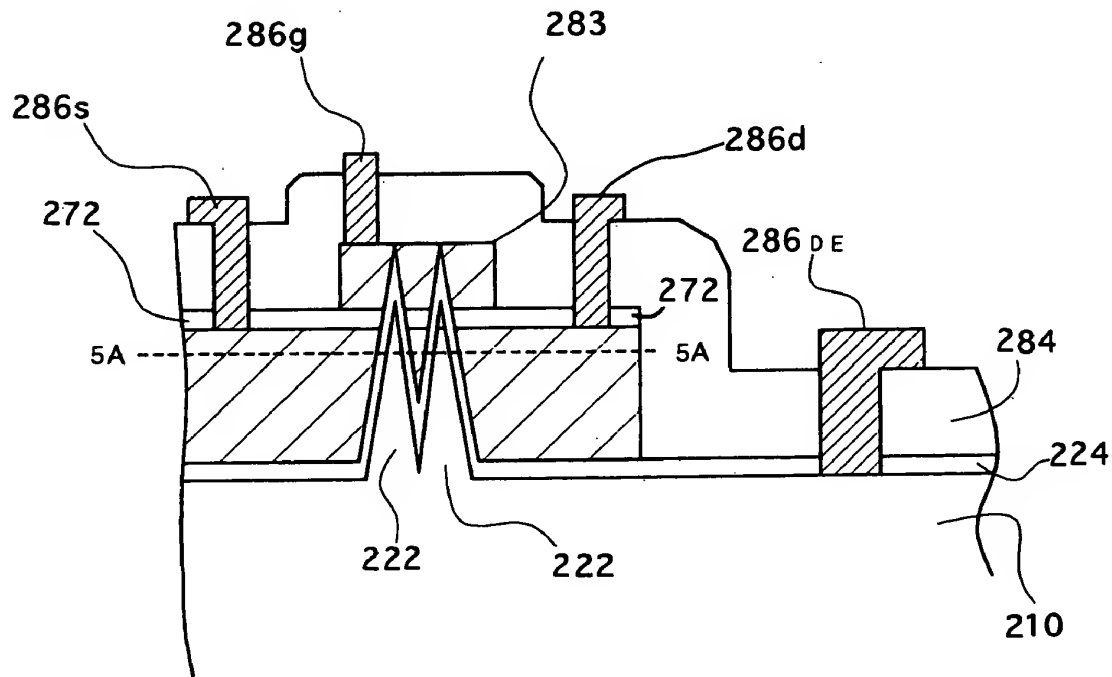


FIG. 29A

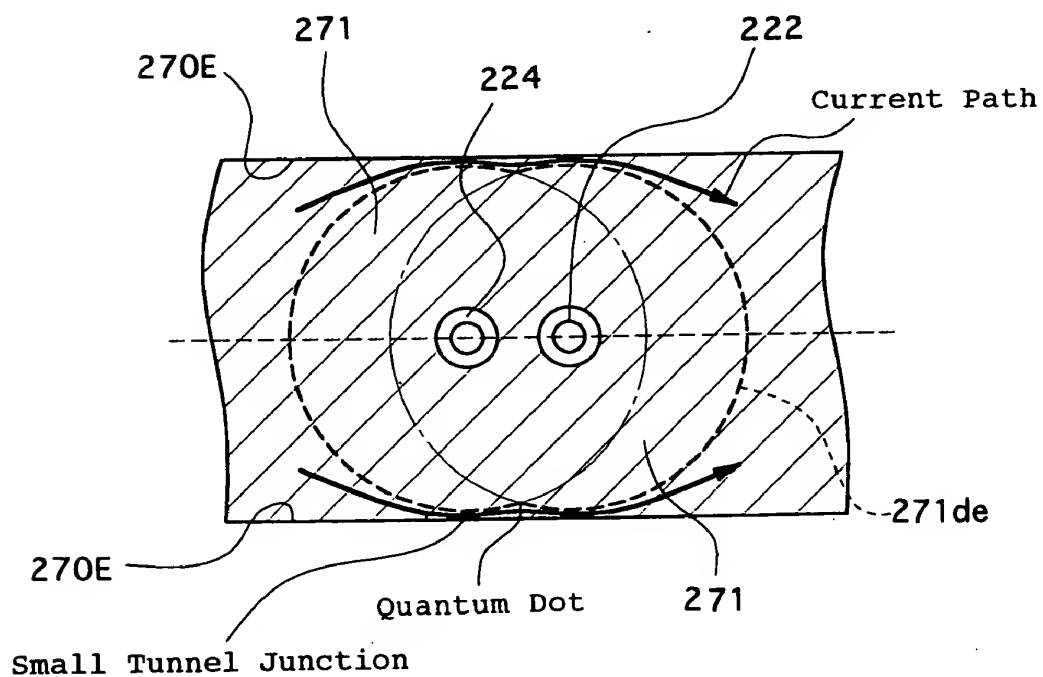


FIG. 29B

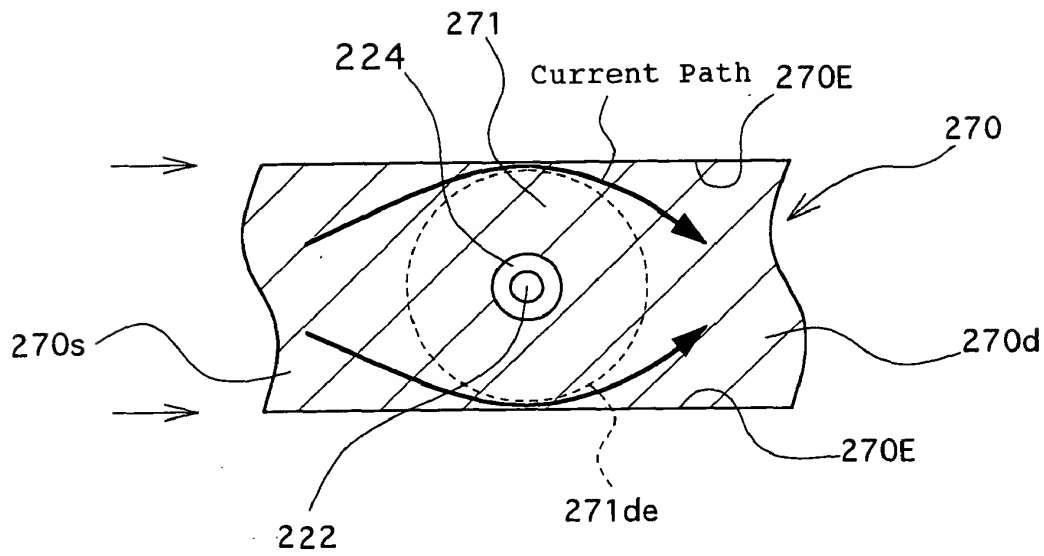


FIG. 30

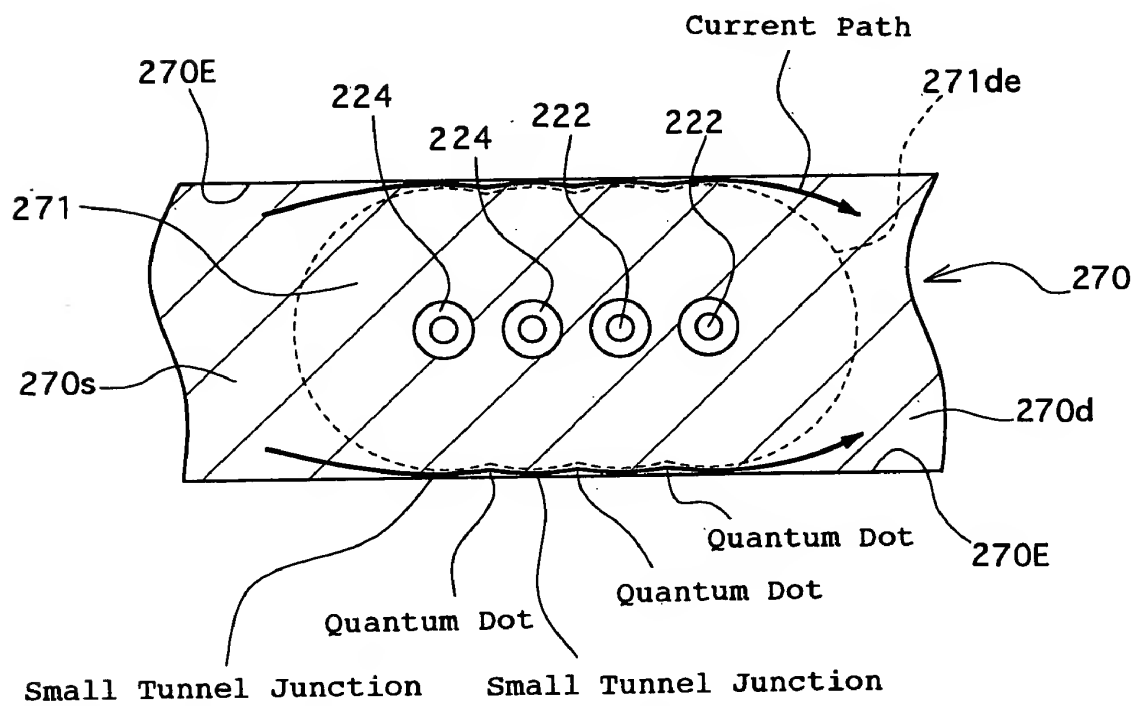


FIG. 31

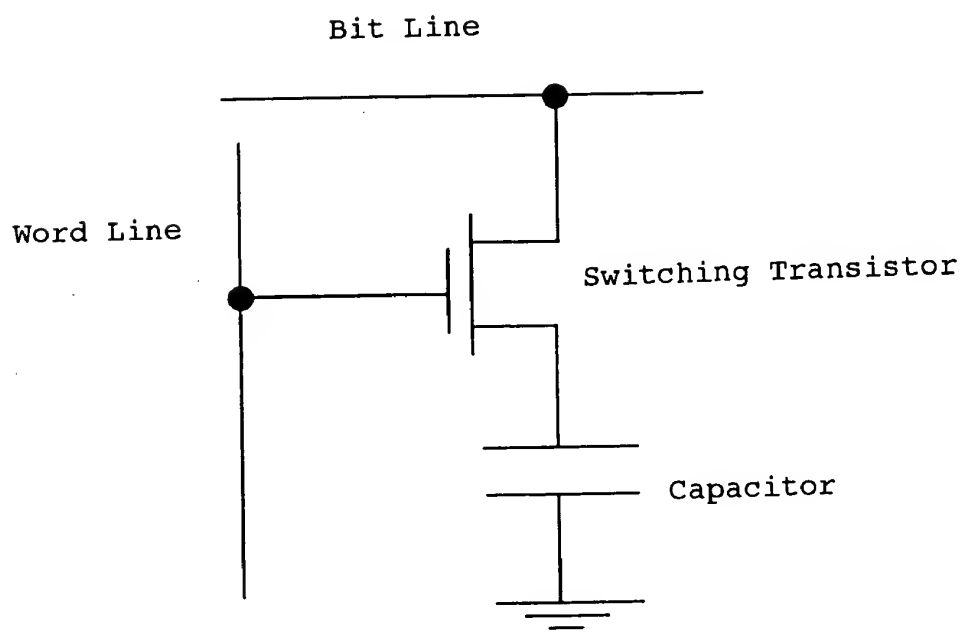


FIG. 32 PRIOR ART

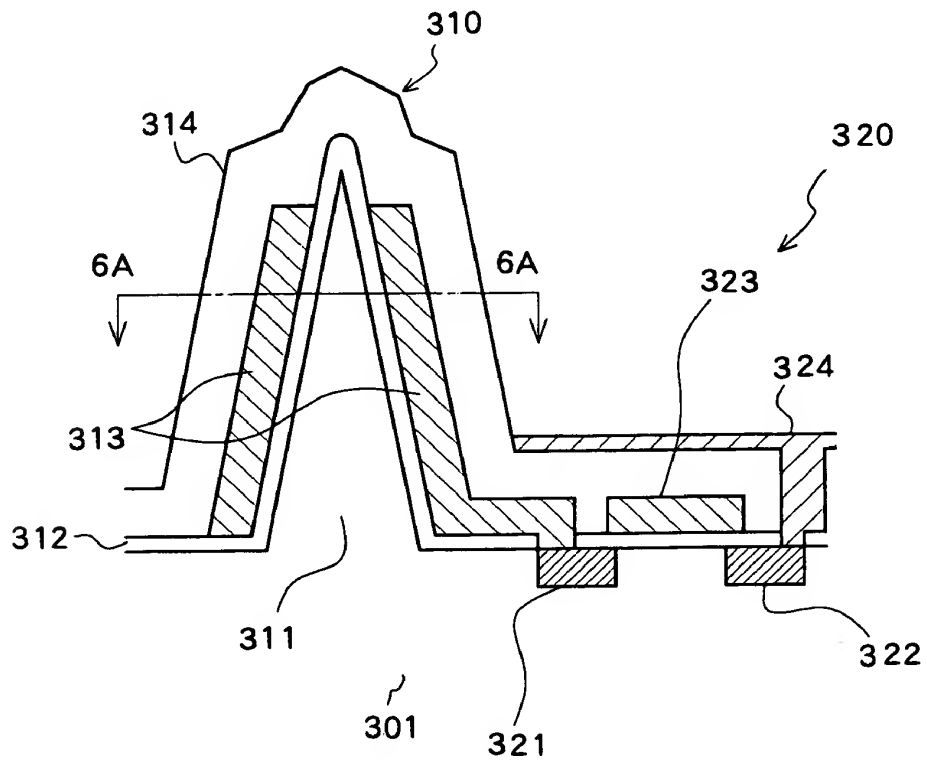


FIG. 33A

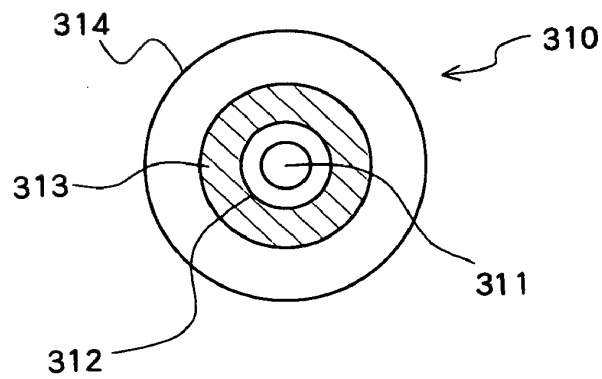


FIG. 33B

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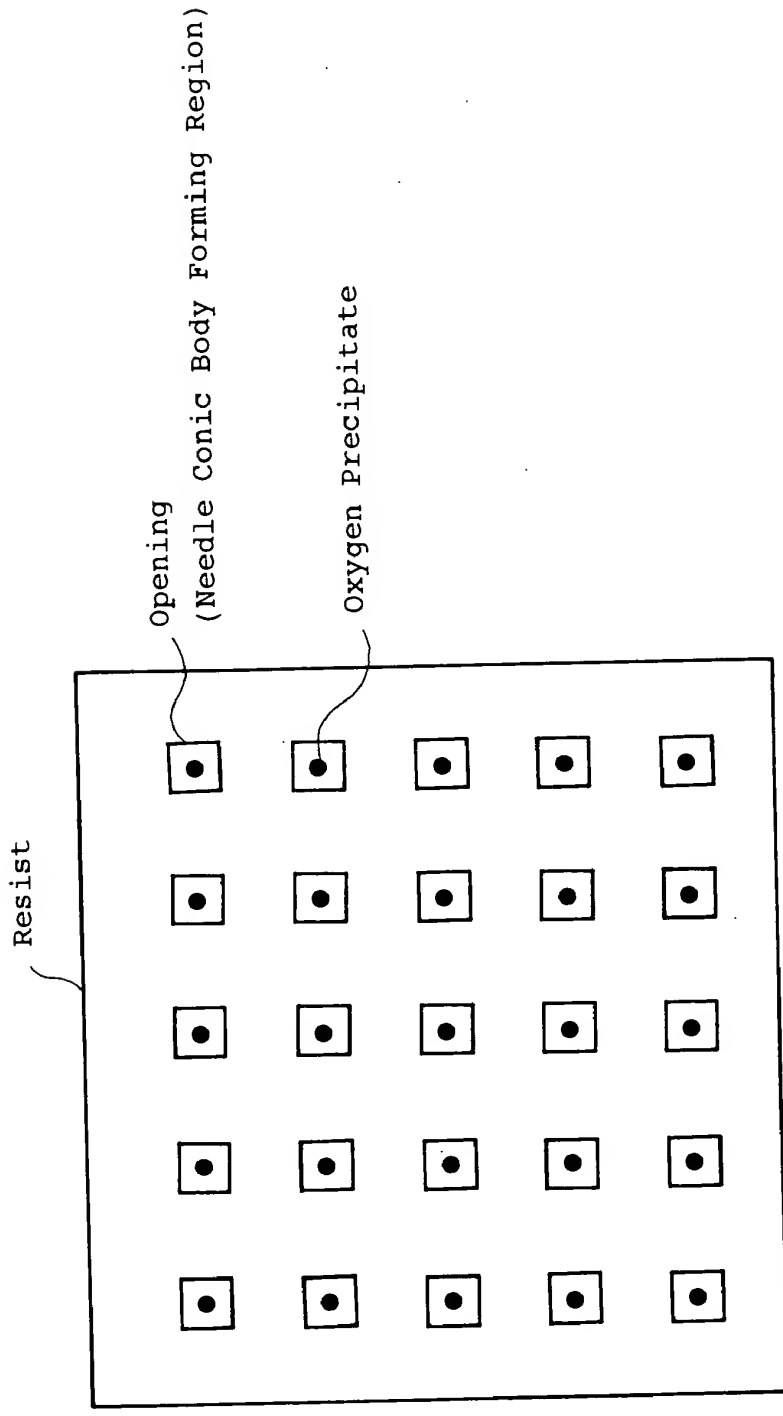
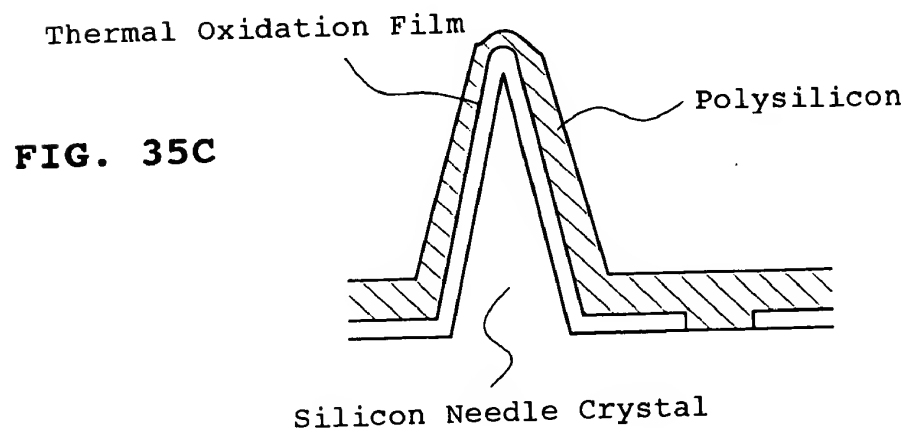
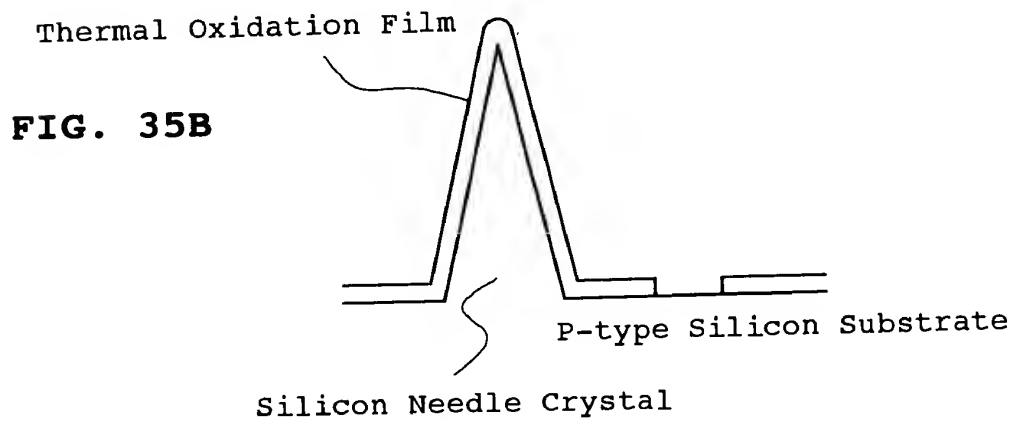
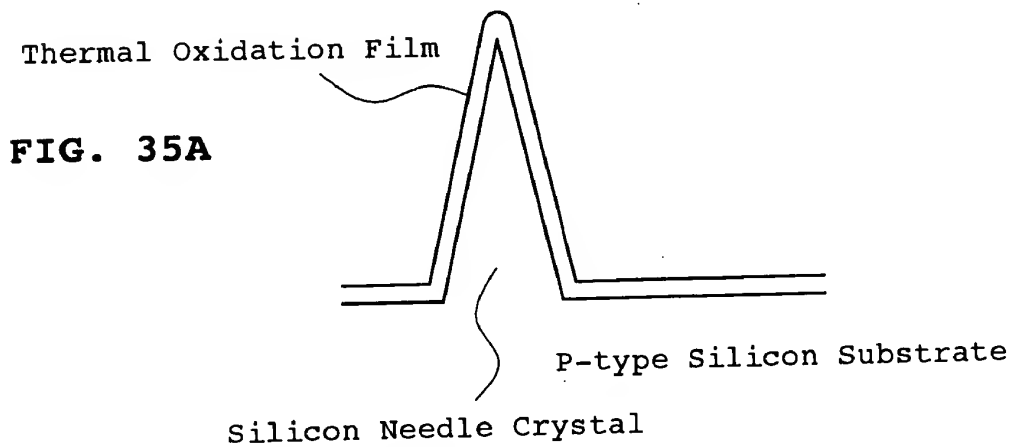
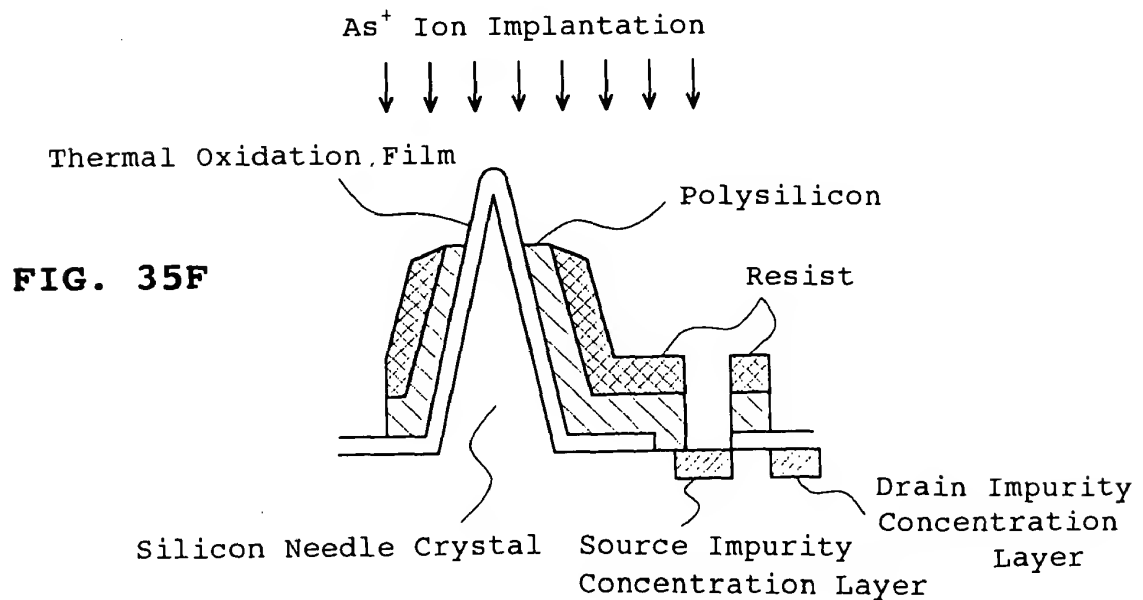
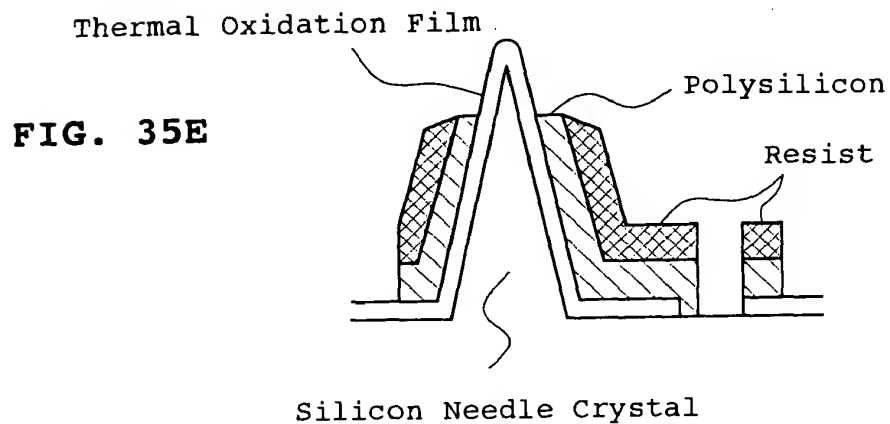
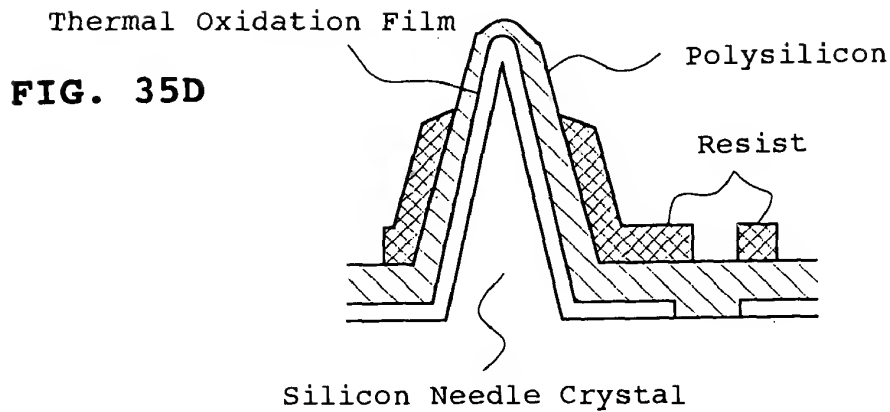
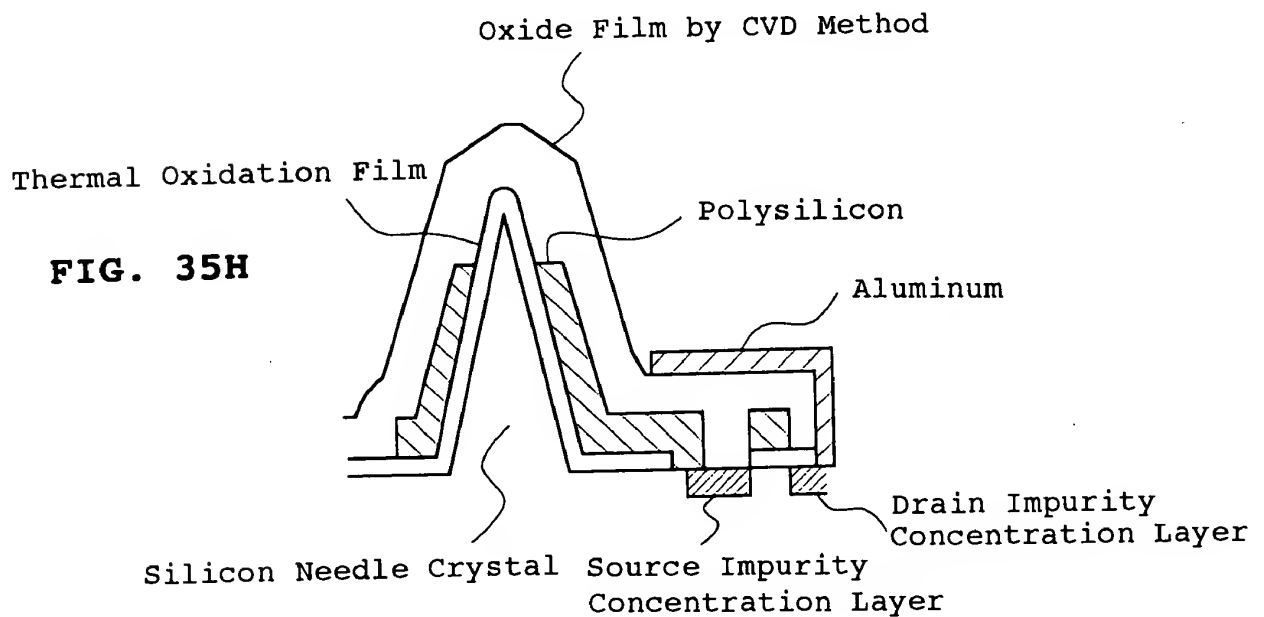
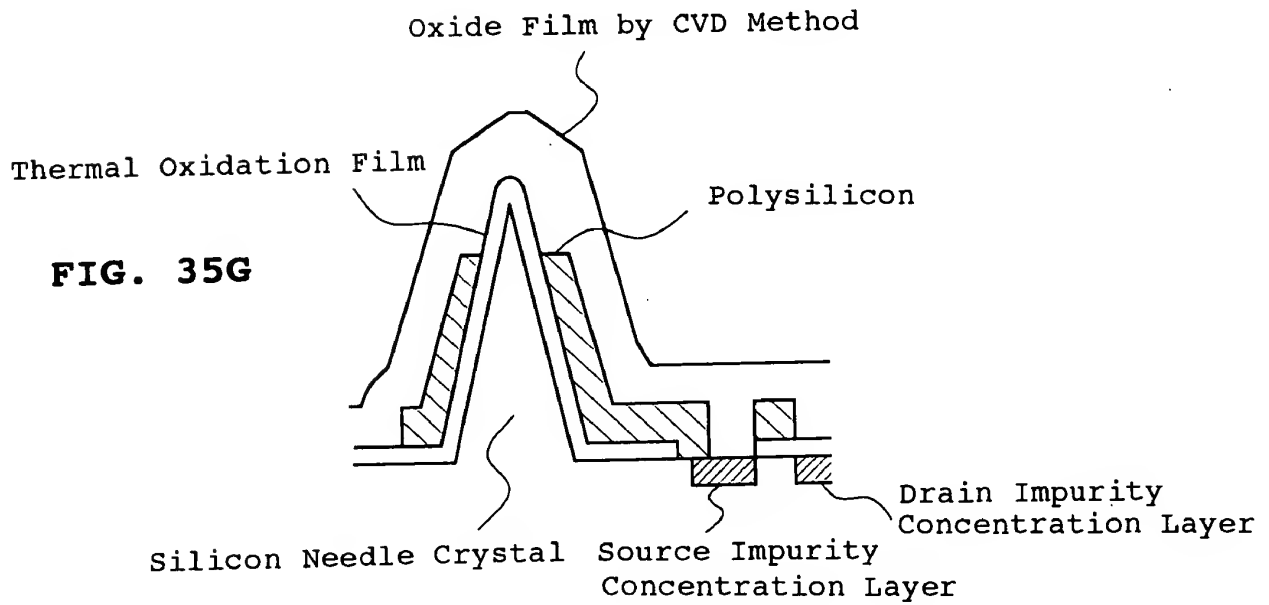


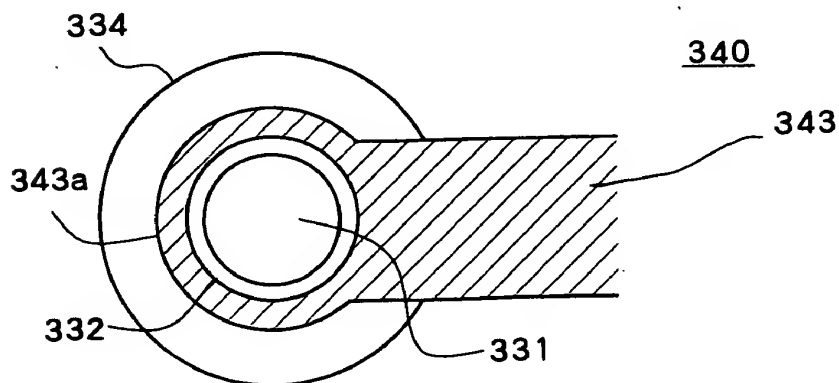
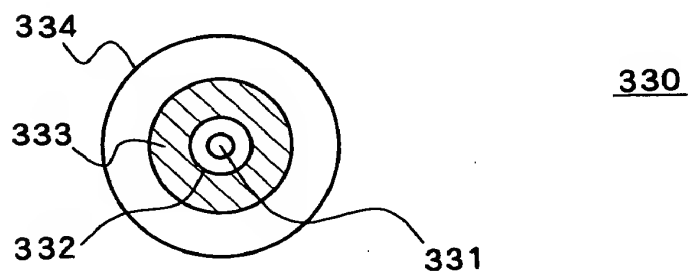
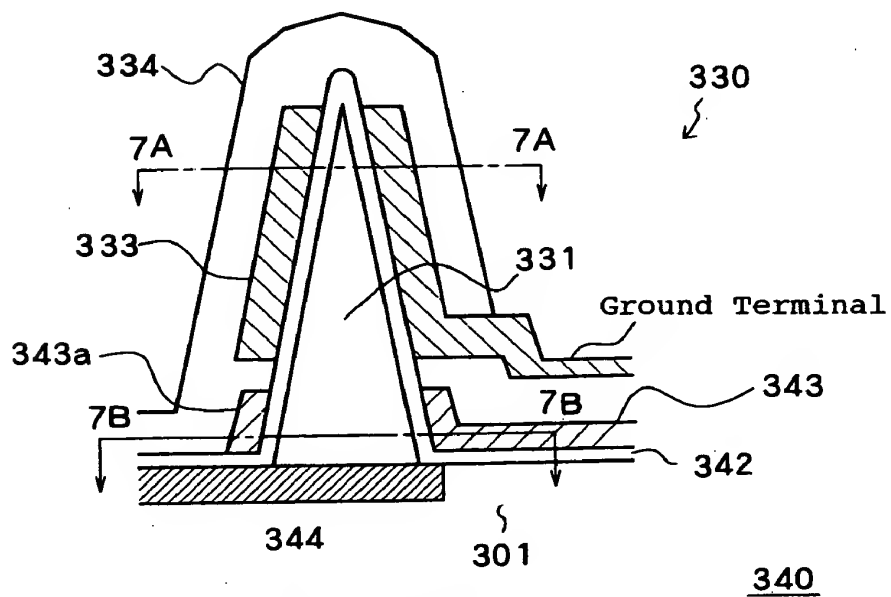
FIG. 34

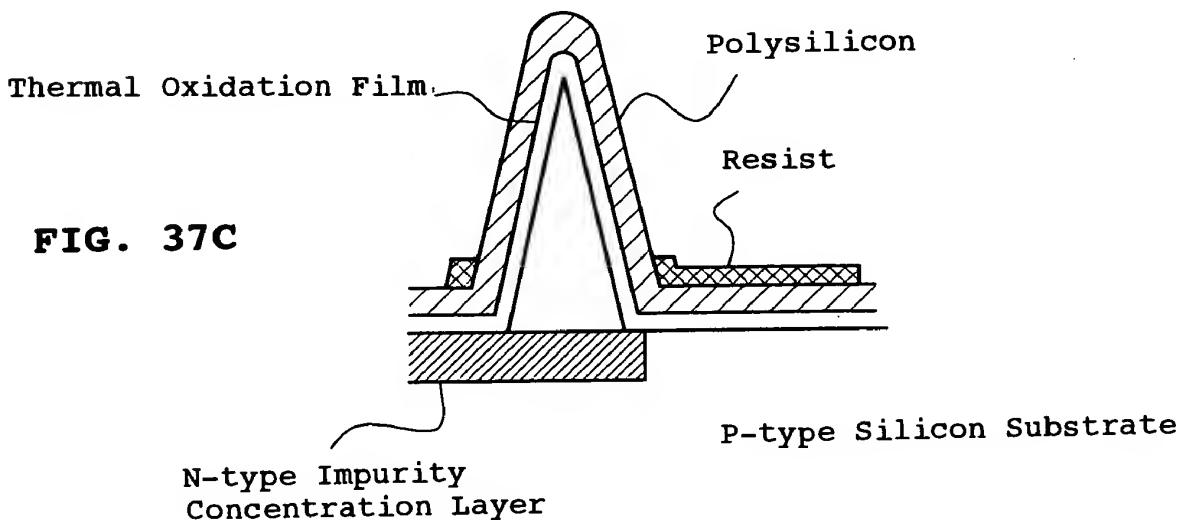
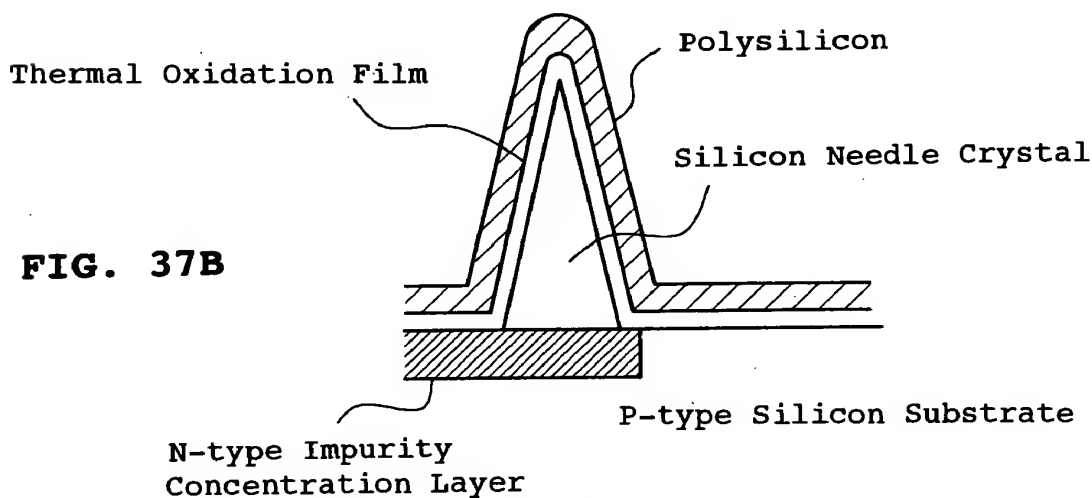
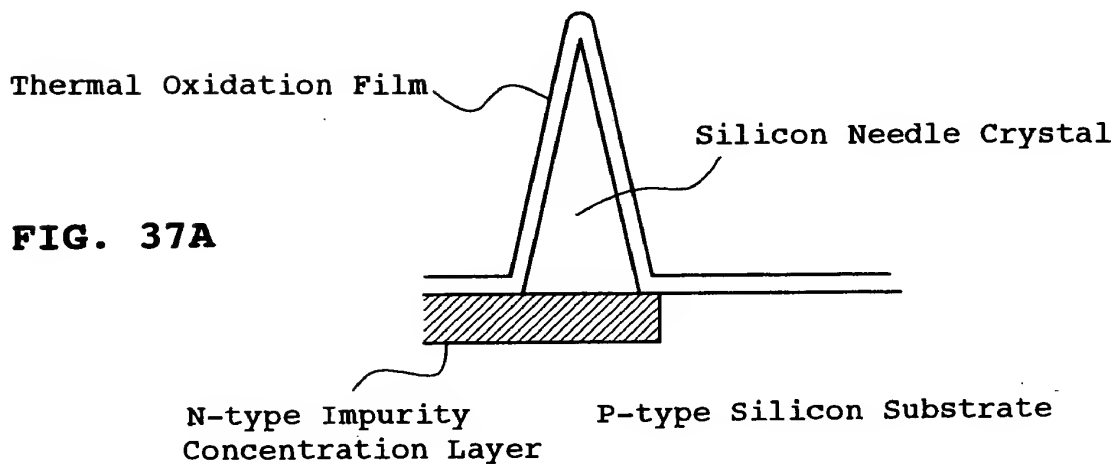


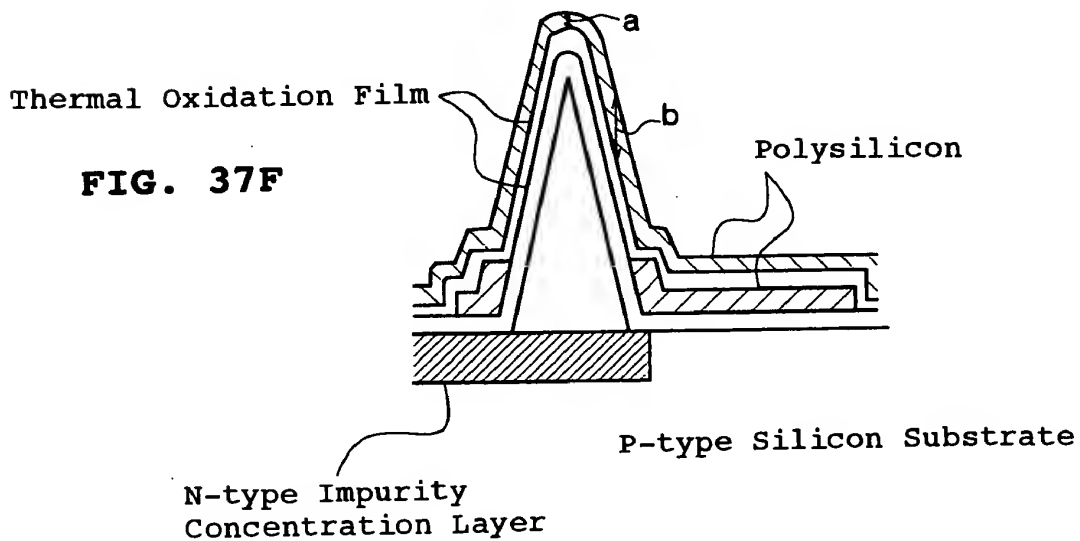
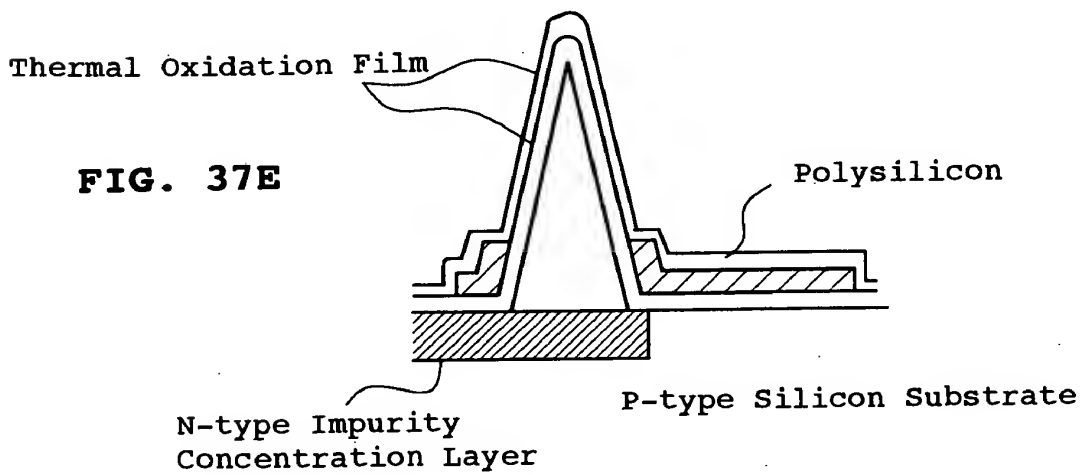
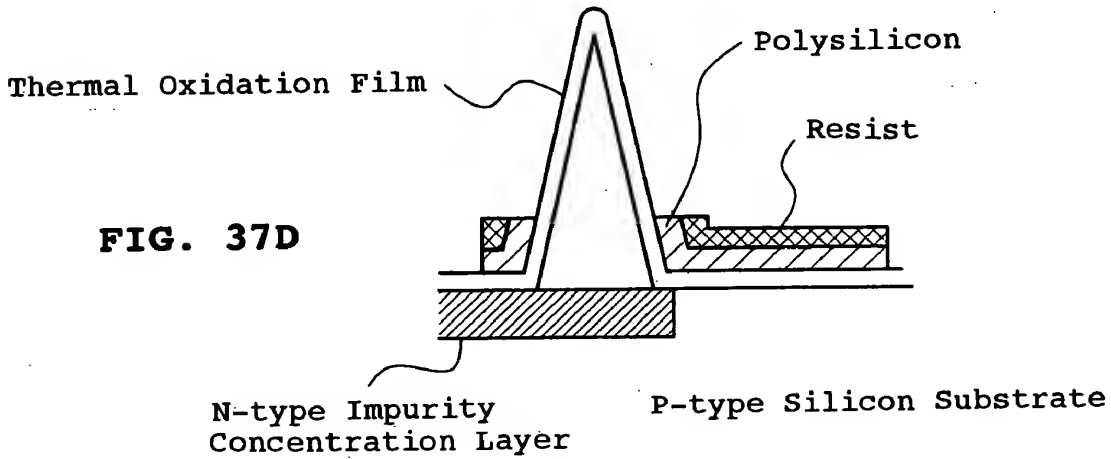


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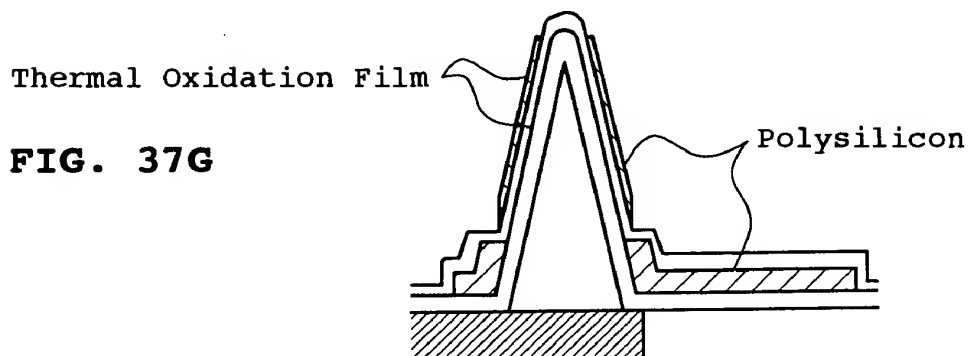


FIG. 37G

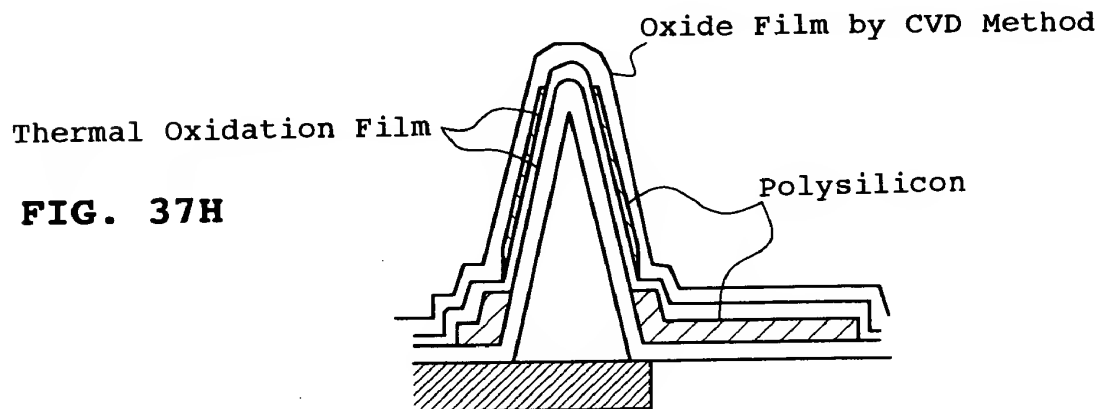


FIG. 37H

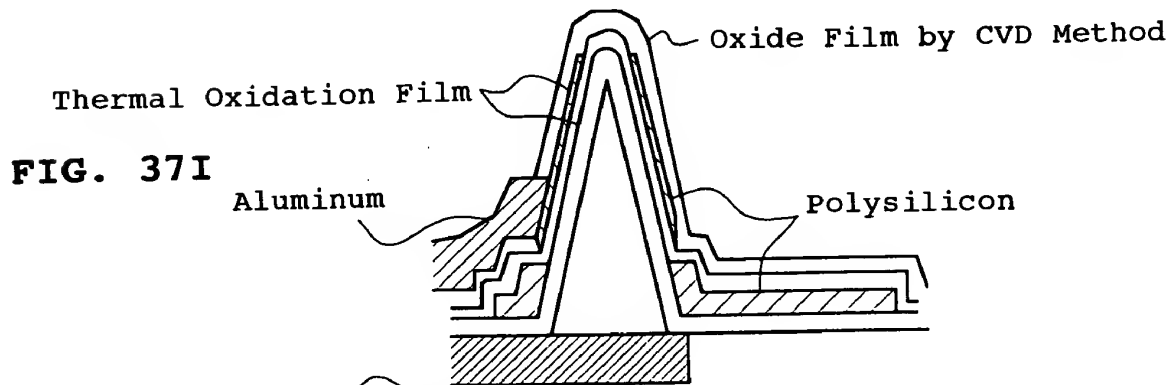
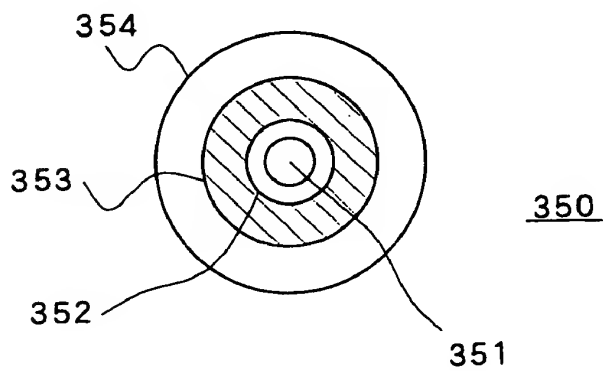
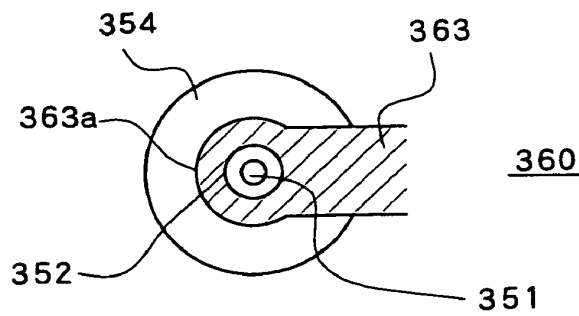
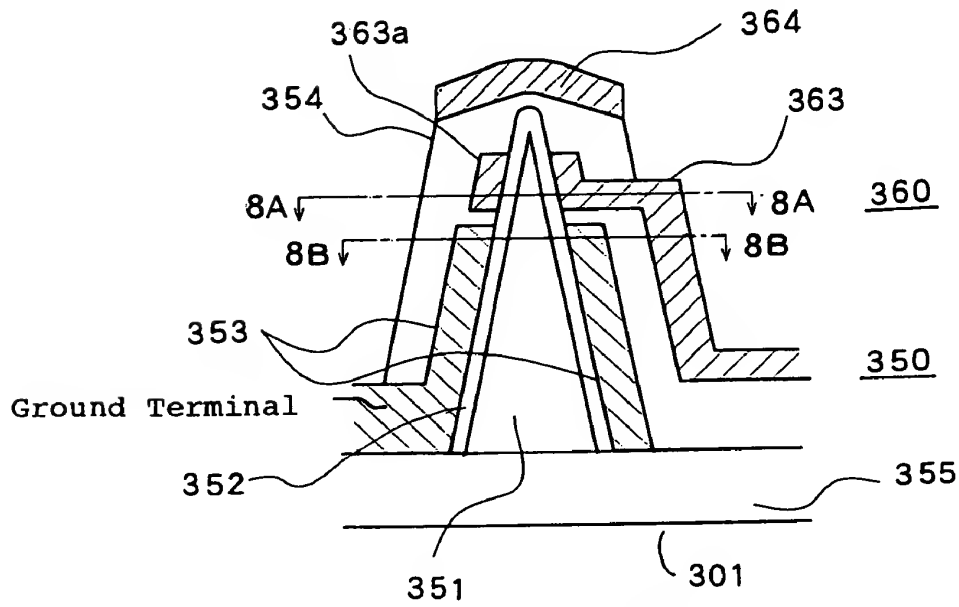
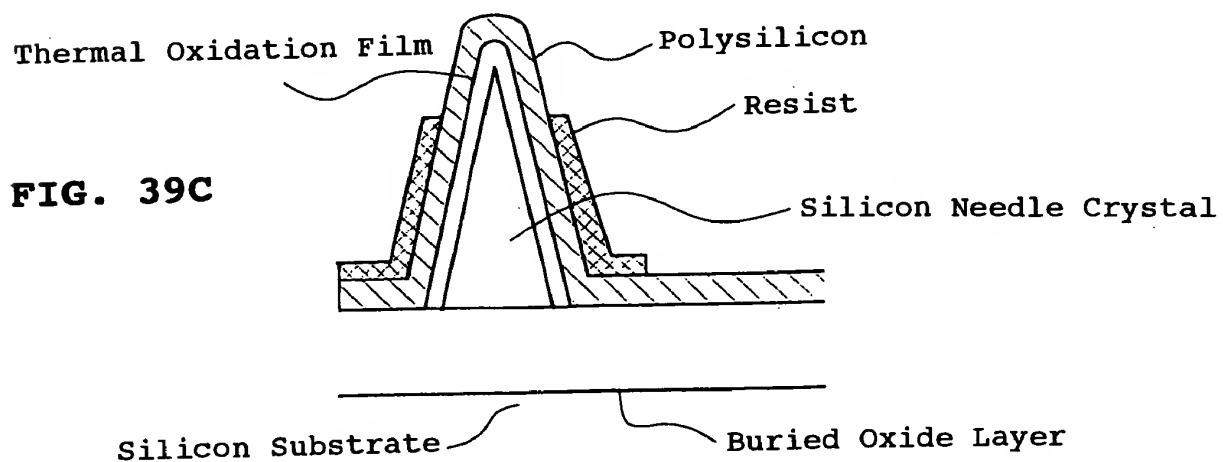
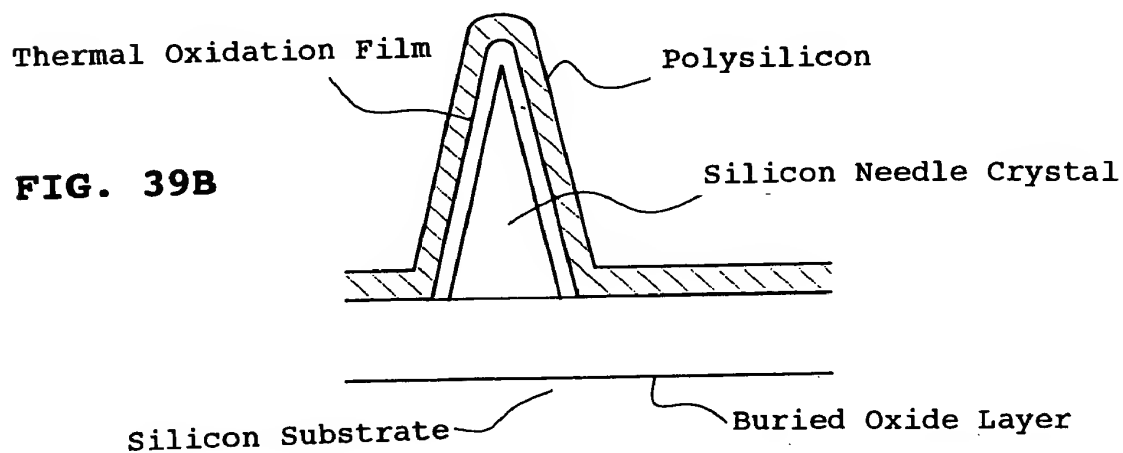
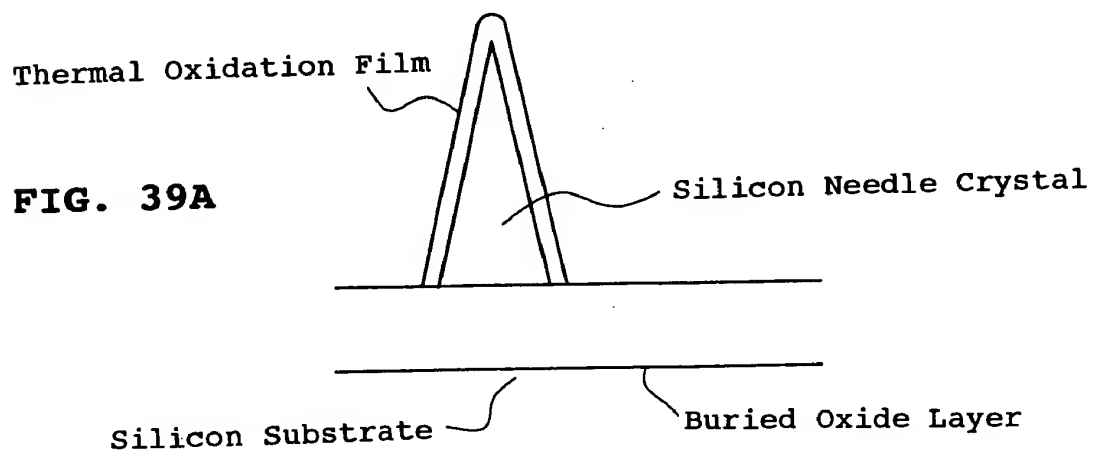


FIG. 37I

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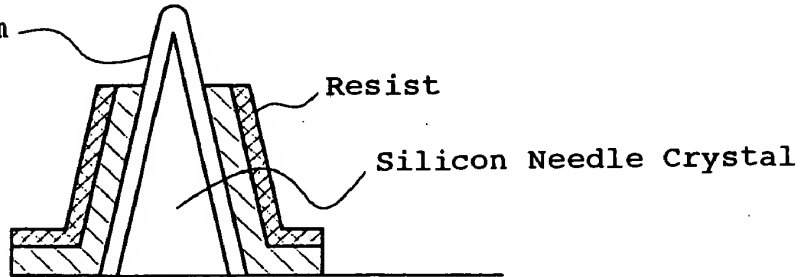




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Thermal Oxidation Film

FIG. 39D

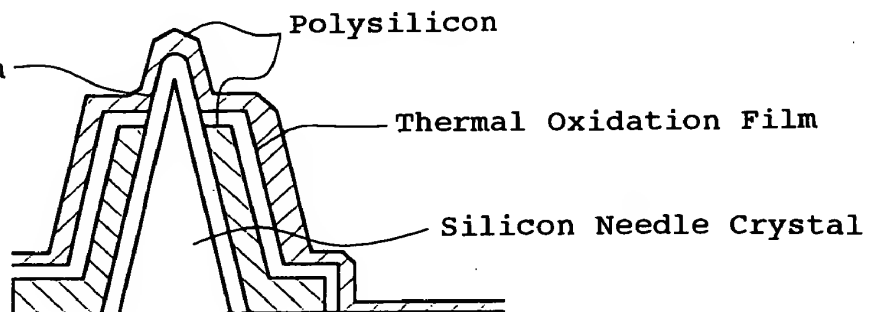


Silicon Substrate

Buried Oxide Layer

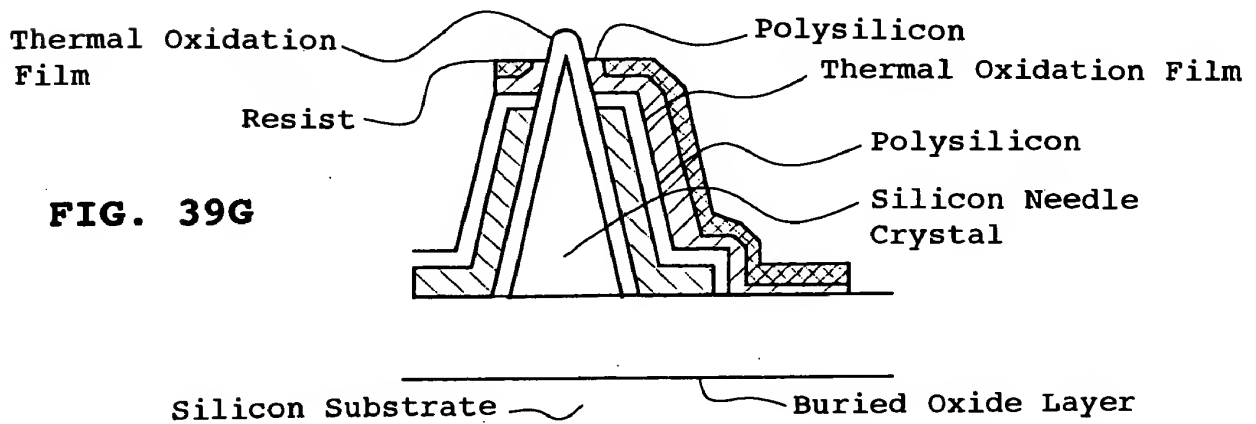
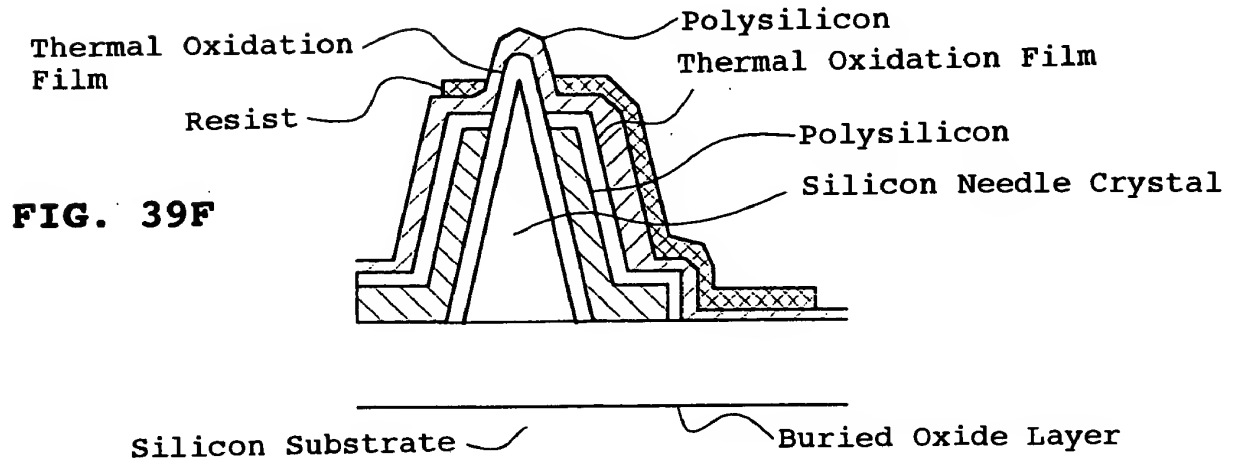
Thermal Oxidation Film

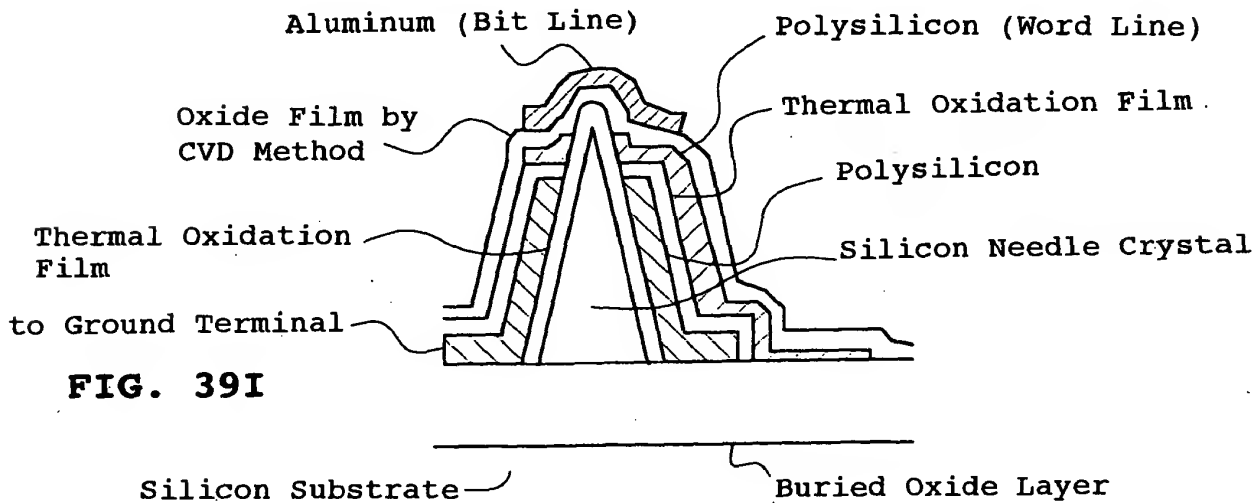
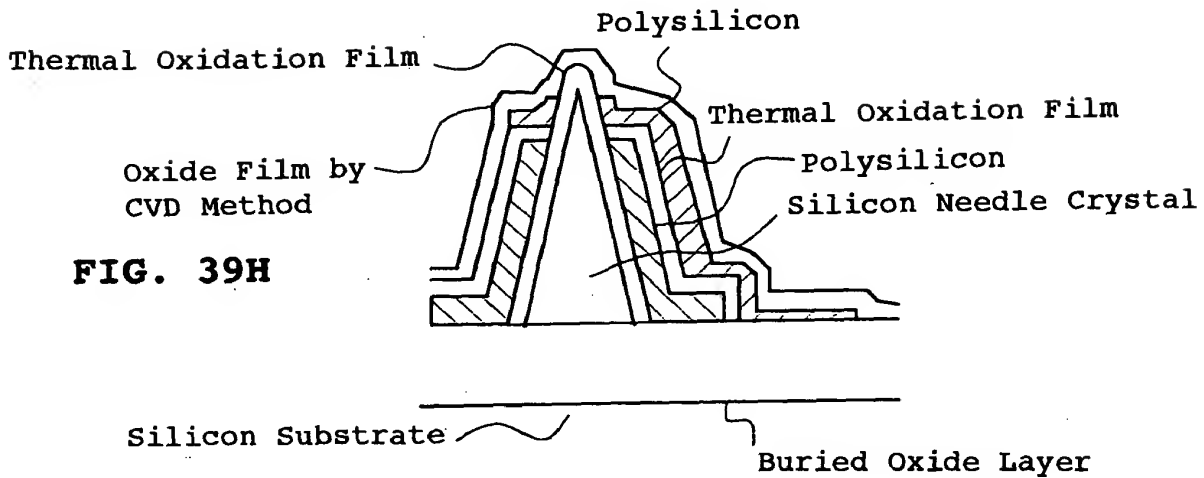
FIG. 39E



Silicon Substrate

Buried Oxide Layer





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